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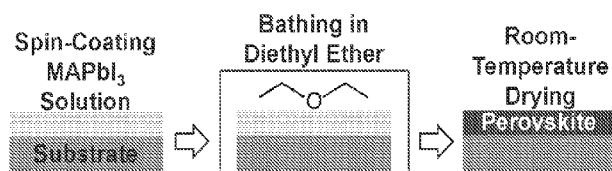
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(54) Title: METHODS OF MAKING COATED SUBSTRATES

Figure 1A



(57) Abstract: Methods' and compositions for making coated substrates using a co-solvent method are disclosed. Embodiments of the present disclosure relate in general to methods and compositions for making thin films of organometallic halides. According to one aspect, organometallic halides are deposited from solution on the surface of a substrate at temperatures between about 10C and 50C. According to one aspect, organometallic halides are deposited from solution on the surface of a substrate at room temperature.

METHODS OF MAKING COATED SUBSTRATES

RELATED APPLICATION DATA

This application claims priority to U.S. Provisional Patent Application No. 62/082,209,
5 filed on November 20, 2014 and is hereby incorporated herein by reference in its entirety for all purposes.

STATEMENT OF GOVERNMENT INTERESTS

This invention was made with government support under DMR-1305913 from National
10 Science Foundation. The Government has certain rights in the invention.

BACKGROUND

Field of the Invention

Embodiments of the present invention relate in general to a method of making a coated
15 substrate for use in a solar cell by forming crystals of an organometallic halide on a substrate surface using a co-solvent method of precipitation.

Description of Related Art

The field of thin-film photovoltaics includes perovskite solar cells that use hybrid perovskites as the light absorber. Methylammonium (*MA*) lead triiodide ($\text{CH}_3\text{NH}_3\text{PbI}_3$ or *MAPbI₃*)
20 is an exemplary perovskite that has been used in solar cells. See, H. J. Snaith, *J. Phys. Chem. Lett.* 4, 3623-3630 (2013); M. D. McGhee, *Nature* 501, 323-325 (2013); M. Grätzel, *Nature Mater.* 13, 838-842 (2014) and H. S. Jung, N.-G. Park, Small DOI: 10.1002/sml.201402767 (2014) in press. *MAPbI₃* possesses a combination of desirable properties, including favorable direct band gap (1.50 to 1.55 eV), large absorption coefficient in the visible spectrum, high carrier mobilities and long
25 carrier-diffusion lengths for both electrons and holes. See G. Xing, N. Mathews, S. Sun, S. S. Lim, Y. M. Lam, M. Grätzel, S. Mhaisalkar, T. C. Sum, *Science* 342, 344-347 (2013); S. D. Stranks, G. E. Eperon, G. Grancini, C. Menelaou, M. J. P. Alcocer, T. Leijtens, L. M. Herz, A. Petrozza, H. J. Snaith, *Science* 342, 341-344 (2013).

This has resulted in *MAPbI₃*-based solar cells with power conversion efficiencies exceeding 20%
30 (see world wide website nrel.gov/ncpv/images/efficiency_chart.jpg as of November 15, 2014) compared to earlier results. See A. Kojima, K. Teshima, Y. Shirai, T. Miyasaka, *J. Am. Chem. Soc.* 131, 6050-6051 (2009).

Typically, the perovskite layer, either as a planar thin film or within mesoscopic oxide scaffolds, is deposited using solution methods including a polar high boiling point solvent. See, H.
35 J. Snaith, *J. Phys. Chem. Lett.* 4, 3623-3630 (2013); M. D. McGhee, *Nature* 501, 323-325 (2013); M. Grätzel, *Nature Mater.* 13, 838-842 (2014) and H. S. Jung, N.-G. Park, Small DOI:

10.1002/smll.201402767 (2014) in press; Y. Zhao, K. Zhu, *J. Phys. Chem. Lett.* DOI: 10.1021/jz501983v (2014). In the case of planar solar cells, the solution-based deposition of the perovskite film is typically accomplished by heating to a high temperature to remove the polar high boiling point solvent thereby causing deposition of perovskite crystals on the substrate surface.

5 Vapor-based methods, either all-vapor or combined with solution-methods, are also used for depositing thin films of perovskite, but the need for vacuum equipment and batch-processing presents fundamental limitations on the manufacturing scalability of these methods. Also, fabrication of full-coverage perovskite films of sub-100 nm thickness is challenging for both the solution-based and the vapor-based methods. Thus, the scalable deposition of high quality

10 perovskite thin films of a wide range of uniform thicknesses remains a challenge. See generally, M. Liu, M. B. Johnston, H. J. Snaith, *Nature* 501, 395-398 (2013); Y. Zhao, K. Zhu, *J. Phys. Chem. Lett.* DOI: 10.1021/jz501983v (2014); M. Liu, M. B. Johnston, H. J. Snaith, *Nature* 501, 395-398 (2013); H. Zhou, Q. Chen, G. Li, S. Luo, T.-B. Song, H.-S. Duan, Z. Hong, J. You, Y. Yang, *Science* 345, 542-546 (2014); J.-H. Im, I. H. Jang, N. Pellet, M. Grätzel, N.-G. Park, *Nature*

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20 *Lett.* 5, 3335-3339 (2014); O. Malinkiewicz, A. Yella, Y. H. Lee, G. M. Espallargas, M. Grätzel, M. K. Nazeeruddin, H. J. Bolnik, *Nature Photon.* 8, 128-132 (2013); L. K. Ono, S. Wang, Y. Kato, S. R. Raga, Y. Qi, *Energy Environ. Sci.* 7, 3989-3993 (2014); Q. Chen, H. Zhou, Z. Hong, S. Luo, H.-S. Duan, H.-H. Wang, Y. Liu, G. Li, Y. Yang, *J. Am. Chem. Soc.* 136, 622-625 (2014); F. Hao, C. C. Stoumpos, Z. Liu, R. P. H. Chang, M. G. Kanatzidis, *Journal of American Chemical*

25 *Society* DOI: 10.1021/ja509245x (2014) in press.

SUMMARY

Embodiments of the present disclosure relate in general to methods and compositions for making thin films of organometallic halides. According to one aspect, organometallic halides are

30 deposited from solution on the surface of a substrate at temperatures between about 10°C and 50°C. According to one aspect, organometallic halides are deposited from solution on the surface of a substrate at room temperature.

According to one aspect, organometallic halides are deposited from a solution including a first solvent provided on the surface of a substrate when the solution on the substrate is contacted

35 with a second solvent which extracts the first solvent from the solution on the surface of the substrate. As a result of the extraction of the first solvent on the surface of the substrate into the

second solvent, the organometallic halides crystallize from solution onto the surface of the substrate. According to one aspect, the organometallic halides are deposited from solution on the surface of a substrate after being contacted with the second solvent at temperatures between about 10°C and 50°C, such as room temperature.

5 According to one aspect, the first solvent has a high boiling point and is a solvent for the organometallic halide. According to one aspect, the second solvent has a low boiling point and is a solvent for the first solvent. According to one aspect, the second solvent is a poor solvent for the organometallic halide or the organometallic halide is insoluble, substantially insoluble or insubstantially soluble in the second solvent. According to one aspect, the organometallic halide
10 has little or no solubility in the second solvent.

According to certain aspects, the present disclosure is directed to a solvent-solvent extraction method that is used to deposit organometallic halides, such as hybrid-perovskites, as thin films on substrates, such as substrates used in solar cells. According to this aspect, solvent-solvent extraction is used to induce crystallization of organometallic halides, such as hybrid-perovskites, and film formation between about 10 seconds and about 5 minutes at a temperature of between about 10°C and 50°C, such as room temperature. Various substrate sizes and surface areas can be used in the practice of the present methods which facilitate deposition of organometallic halide thin films over large surface areas making the methods useful for many different applications such as tandem solar cells or any other large surface area that would benefit from a continuous organometallic halide thin film.

Further features and advantages of certain embodiments of the present disclosure will become more fully apparent in the following description of the embodiments and drawings thereof, and from the claims.

25 BRIEF DESCRIPTION OF THE DRAWINGS

The patent or application file contains at least one drawing executed in color. Copies of this patent or patent application publication with color drawing(s) will be provided by the Office upon request and payment of the necessary fee. The foregoing and other features and advantages of the present invention will be more fully understood from the following detailed description of illustrative embodiments taken in conjunction with the accompanying drawings in which:

Fig. 1A is a schematic illustration showing the SSE process for the room-temperature deposition of hybrid perovskite thin films. Fig. 1B depicts an indexed XRD pattern. Fig. 1C depicts low-magnification SEM micrographs of the top surface of a MAPbI_3 perovskite film deposited on a glass substrate using the SSE method. Fig. 1D depicts high-magnification SEM micrographs of the top surface of a MAPbI_3 perovskite film deposited on a glass substrate using the SSE method.

Fig. 2(A)-2(C) are photographs at various stages of the solvent-solvent extraction process described herein.

Fig. 3 are photographs at various stages of the solvent-solvent extraction process described herein.

5 Fig. 4 are photographs at various stages of the solvent-solvent extraction process described herein.

Fig. 5A depicts a cross-sectional image of MAPbI_3 perovskite films deposited on a TiO_2 -blocking-layer coated FTO-glass substrate using SEM (~ 250 nm film thickness). Fig. 5B depicts a cross-sectional image of MAPbI_3 perovskite films deposited on a TiO_2 -blocking-layer coated FTO-glass substrate using bright-field TEM (~ 80 nm film thickness). The light contrast at the interface between the FTO and the perovskite is the TiO_2 blocking layer. Fig. 5C depicts a high-resolution TEM plan view image of a MAPbI_3 perovskite film deposited on a TEM grid using the SSE method showing lattice imaging and defects. Fig. 5D shows shows 100 or 010 lattice planes, and other fine structure. Fig. 5E is a large area image ($40 \times 40 \text{ } \mu\text{m}^2$) AFM image of a MAPbI_3 perovskite film
 10 (~ 250 nm thickness) deposited on a TiO_2 -blocking-layer coated FTO-glass substrate. Fig. 5F is a small area image ($2 \times 2 \text{ } \mu\text{m}^2$) AFM image of a MAPbI_3 perovskite film (~ 250 nm thickness) deposited on a TiO_2 -blocking-layer coated FTO-glass substrate. Fig. 5G is a photograph of a MAPbI_3 perovskite film (~ 350 nm thickness) deposited on a TiO_2 -blocking-layer coated FTO-glass substrate (dashed $5 \times 6 \text{ cm}^2$ rectangle) held in bright sunshine. Fig. 2H is a photograph of the same
 15 film showing high reflectivity.
 20

Fig. 6(A)-6(D) are SEM images of perovskite films of various thicknesses.

Fig. 7 is a TEM image of a perovskite film deposited on a TiO_2 blocking layer coated FTO glass substrate.

Fig. 8(A)-8(D) are TEM images of a perovskite-based solar cell.

25 Fig. 9 is an elemental EDS mapping of the solar cell of Fig. 8(A)-8(D).

Fig. 10(A)-10(C) are graphs of transmission, reflection and absorption versus wavelength.

Fig. 11A depicts XRD patterns from an MAPbI_3 precursor as-spin-coated film (in NMP) on a glass substrate. Fig. 11B depicts XRD patterns from an MAPbI_3 precursor as-spin-coated film (in NMP) on a glass substrate after 2 s of NMP extraction by dimethyl ether solvent at room
 30 temperature. Fig. 11C depicts XRD patterns from an MAPbI_3 precursor as-spin-coated film (in NMP) on a glass substrate after 2 min of NMP extraction by dimethyl ether solvent at room temperature. Note the sharpening of the XRD peaks in Fig. 11C. Fig. 11D is an FTIR spectra corresponding to Fig. 11B after 2 s (red) and Fig. 11C after 2 min (black). The C=O stretching band at $\sim 1700 \text{ cm}^{-1}$ observed in the 2-s film is marked. Fig. 11E is a proposed schematic
 35 illustration of an exemplary solvent-solvent extraction mechanism.

Fig. 12A depicts current density (J) – voltage (V) characteristics of solar cells based on MAPbI_3 perovskite thin films with different thicknesses deposited by a solvent-solvent extraction method as described herein at room temperature under simulated one-sun AM 1.5G ($100 \text{ mW} \cdot \text{cm}^{-2}$) illumination (0.16 cm^2 active area). The dashed red J - V curve is for a solar cell with highest PCE of 15.2%. Fig. 12B is a graph of external quantum efficiency (EQE) as a function of wavelength for the solar cells in Fig. 12A.

Fig. 13 is a graph of PCE versus time.

Fig. 14 is a graph of PCE versus MAPbI_3 thickness.

Fig. 15(A) is a Nyquist plot of impedance resistance. Fig. 15(B) is a plot of recombination resistance as a function of voltage.

Fig. 16(A)-16(D) are XRD patterns from $\text{MAPbI}_{(3-x)}\text{Br}_x$ perovskite films deposited on glass substrates.

Fig. 17 are photographs of $\text{MAPbI}_{(3-x)}\text{Br}_x$ perovskite films deposited on TiO_2 blocking layer coated FTO-glass substrates.

Fig. 18 is a graph of J-V characteristics and extracted performance parameters for a solar cell having a perovskite film deposited using the methods described herein.

DETAILED DESCRIPTION

Embodiments of the present disclosure are directed to the formation of a layer or film or coating of an organometallic halide on the surface of a substrate. According to one aspect, the organometallic halide may be referred to as a pervoskite or a hybrid pervoskite. Pervoskites and hybrid pervoskites and the three dimensional or two dimensional crystal structures they form are known to those of skill in the art and are extensively described in Cheng, et al., *CrystEngComm*, 2010, 12, 2646-2662 hereby incorporated by reference in its entirety for all purposes.

According to one aspect, a method of making a coated substrate is provided that includes contacting a surface of a substrate having a coating of a solution of a first solvent and an organometallic halide thereon with a second solvent, wherein the organometallic halide is insoluble in the second solvent and the first solvent is miscible with the second solvent, wherein the first solvent is extracted from the coating of the solution into the second solvent, and wherein the organometallic halide precipitates from the solution onto the surface of the substrate forming an organometallic halide coating on the substrate. According to one aspect, the coating of the solution is formed by applying the solution to the surface of the substrate. The solution may be applied to the substrate by methods known to those of skill in the art such as spin coating, dip coating, spray coating, ink jet printing or the like. According to one aspect, a portion of the first solvent may be removed such as by evaporation. In this manner, the organometallic halide becomes more concentrated in the solution which is on the surface of the substrate.

Organometallic halides within the scope of the present disclosure are compounds represented by RMe_nX_y wherein Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb; X is one or more of I, Br, Cl; y is 3 or $(3n+1)$; n is 1, 2, 3, 4, 5; R is an organic group, CH_3NH_3 , $\text{NH}_3\text{CH}=\text{CH}_2$, Cs, $(\text{R}'\text{-NH}_3)_2$, $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ or $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$; and R' is alkyl, C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$; with the proviso that when y is 3, n is 1, Me is Pb, Sn, Ge, Eu or Yb and R is an organic group, CH_3NH_3 or $\text{NH}_3\text{CH}=\text{CH}_2$, or Cs, and further with the proviso that when y is $(3n+1)$ and n is 1, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb, and R is $(\text{R}'\text{-NH}_3)_2$ or $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ and further with the proviso that when y is $(3n+1)$ and n is 2, 3, 4, or 5, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb and R is $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$.

Organometallic halides within the scope of the present disclosure are compounds represented by RMeX_3 wherein R is an organic group or Cs, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of I, Br, Cl. According to one aspect, the organic group may be CH_3NH_3 or $\text{NH}_3\text{CH}=\text{CH}_2$. An exemplary organometallic halide is $\text{CH}_3\text{NH}_3\text{PbI}_3$.

Organometallic halides within the scope of the present disclosure are compounds represented by $(\text{R-NH}_3)_2\text{MeX}_4$ wherein R is alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is a transition metal or a rare earth metal and X is one or more of Cl, Br, or I. According to one aspect, R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.

Organometallic halides within the scope of the present disclosure are compounds represented by $(\text{NH}_3\text{-R-NH}_3)_2\text{MeX}_4$ wherein R is alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is a transition metal or a rare earth metal and X is one or more of Cl, Br, or I. According to one aspect, R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_3$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.

Organometallic halides within the scope of the present disclosure are compounds represented by $(\text{R}'\text{NH}_3)_2(\text{R})_{(n-1)}\text{Me}_n\text{X}_{(3n+1)}$ wherein R' is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, R is Cs, CH_3NH_3 or $\text{NH}_3\text{CH}=\text{CH}_2$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb, X is one or more of Cl, Br, or I and n is 2, 3, 4, or 5.

According to one aspect, the first solvent is a polar solvent having a boiling point within the range of 100 °C and 300 °C. Exemplary first solvents include dimethylformamide, dimethylsulfoxide, γ -butyrolactone, n-methyl-2-pyrrolidone, dimethylacetamide or dimethylphosphoramidate and the like.

According to one aspect, the second solvent is a nonpolar solvent having a boiling point within the range of 0 °C and 100 °C. Exemplary second solvents include diethyl ether, pentane, cyclopentane, hexane, cyclohexane, benzene, chloroform, carbon disulphide, carbon tetrachloride, dibutyl ether, diethylamine, trichloroethylene, triethylamine or dichloromethane and the like.

According to one aspect, the organometallic halide is precipitated onto the surface of the substrate forming a coating on the substrate to result in a coated substrate at a temperature between 10 °C and below 70 °C, between 10 °C and 50 °C, between 20 °C and 30 °C or between 18 °C and 23 °C.

5 Substrates according to the present disclosure are those known to those of skill in the art as being useful in the manufacture of solar cells. Such substrates can also include one or more of a polymer, glass, ceramic, or metal. Substrates according to the present disclosure can be of any three dimensional configuration as desired. An exemplary substrate is a planar substrate.

According to aspects of the present disclosure, the first solvent and the second solvent are
10 selected such that the first solvent is a solvent for the organometallic halide and is miscible with the second solvent. The second solvent is selected such that it is a poor solvent for the organometallic halide. When contacted together, the second solvent extracts the first solvent from the solution and into the second solvent to form a miscible mixture of the second solvent and the first solvent and the organometallic halide crystallizes from solution onto the surface of the substrate forming an
15 organometallic halide coating on the substrate. According to one aspect, after the solution including the first solvent and the organometallic halide is applied to the surface of the substrate, the first solvent is contacted with the second solvent by immersing the substrate in a volume of the second solvent. Other methods may be employed such as dipping the substrate into a volume of the second solvent, spin casting the second solvent onto the surface of the substrate, spraying the
20 first solvent onto the surface of the substrate or any other method known to those of skill in the art for applying a liquid to the surface of a substrate. According to one aspect, immersing the substrate in a volume of the second solvent is exemplary as it facilitates the removal or extraction of the first solvent from the solution applied to the surface of the substrate.

After formation of the organometallic halide coating on the substrate, either the first
25 solvent or the second solvent, if present, is removed from the coated substrate, such as by drying at room temperature or a temperature at which the solvent may evaporate from the coated substrate. An exemplary temperature is between 18°C and 100°C. Accordingly, if the substrate is immersed in a volume of the second solvent, the substrate is removed and the substrate is then dried.

According to one aspect, the methods described herein deposit high quality hybrid
30 perovskite thin films or coatings over large areas, such as for high-performance perovskite solar cells, as are known in the art. The thin films, layers or coatings produced by the present method exhibit advantageous phase purity, thickness, uniformity, smoothness and semitransparency compared with perovskite coatings produced by prior methods, such as high temperature methods. According to one aspect, the films, layers or coatings have a thickness of between 20 nm and 2 µm.
35 The thin films, layers or coatings are produced rapidly, i.e. within between 1 second and 5 minutes, between 2 seconds and 3 minutes, or between 30 seconds and 2 minutes. According to one aspect,

the film, layer or coating produced by the methods described herein has an average uniform surface roughness of between about 1 nm and 20 nm (root mean square) as measured using an atomic force microscope.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 5 the coating is a room temperature precipitate of an organometallic halide having the formula RMe_nX_y wherein Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb; X is one or more of I, Br, Cl; y is 3 or $(3n+1)$; n is 1, 2, 3, 4, 5; R is an organic group, CH_3NH_3 , $NH_3CH=CH_2$, Cs, $(R'-NH_3)_2$, $(NH_3-R'-NH_3)_2$ or $(R'-NH_3)_2R_{(n-1)}$; and R' is alkyl, C_1 to C_4 alkyl or $C_6H_5C_2H_4$; with the proviso that when y is 3, n is 1, Me is Pb, Sn, Ge, Eu or Yb and R is an organic group, CH_3NH_3 or
 10 $NH_3CH=CH_2$, or Cs, and further with the proviso that when y is $(3n+1)$ and n is 1, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb, and R is $(R'-NH_3)_2$ or $(NH_3-R'-NH_3)_2$ and further with the proviso that when y is $(3n+1)$ and n is 2, 3, 4, or 5, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb and R is $(R'-NH_3)_2R_{(n-1)}$.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 15 the coating is a room temperature precipitate of an organometallic halide having the formula $RMeX_3$ wherein R is Cs, CH_3NH_3 or $NH_2CH=CH_2$, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of Cl, Br, or I.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 the coating is a co-solvent precipitate of an organometallic halide having the formula $RMeX_3$
 20 wherein R is Cs, CH_3NH_3 or $NH_2CH=CH_2$, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of Cl, Br, or I.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 the coating is a room temperature precipitate of an organometallic halide having the formula $(R-NH_3)_2MeX_4$ wherein R is C_1 to C_4 alkyl or $C_6H_5C_2H_4$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb,
 25 Eu or Yb and X is one or more of Cl, Br, or I.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 the coating is a co-solvent precipitate of an organometallic halide having the formula $(R-NH_3)_2MeX_4$ wherein R is C_1 to C_4 alkyl or $C_6H_5C_2H_4$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb,
 Eu or Yb and X is one or more of Cl, Br, or I.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 30 the coating is a room temperature precipitate of an organometallic halide having the formula $(NH_3-R-NH_3)_2MeX_4$ wherein R is C_1 to C_4 alkyl or $C_6H_5C_2H_3$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.

According to one aspect, a solar cell is provided that includes a coated substrate wherein
 35 the coating is a co-solvent precipitate of an organometallic halide having the formula $(NH_3-R-$

$(\text{NH}_3)_2\text{MeX}_4$ wherein R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_3$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.

According to one aspect, a solar cell is provided that includes a coated substrate wherein the coating is a room temperature precipitate of an organometallic halide having the formula
 5 $(\text{R}'\text{NH}_3)_2(\text{R})_{(n-1)}\text{Me}_n\text{X}_{(3n+1)}$ wherein R' is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, R is Cs, CH_3NH_3 or $\text{NH}_2\text{CH}=\text{CH}_2$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb, X is one or more of Cl, Br, or I and n is 2, 3, 4, or 5.

According to one aspect, a solar cell is provided that includes a coated substrate wherein the coating is a co-solvent precipitate of an organometallic halide having the formula
 10 $(\text{R}'\text{NH}_3)_2(\text{R})_{(n-1)}\text{Me}_n\text{X}_{(3n+1)}$ wherein R' is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, R is Cs, CH_3NH_3 or $\text{NH}_2\text{CH}=\text{CH}_2$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb, X is one or more of Cl, Br, or I and n is 2, 3, 4, or 5.

According to one aspect, a coated substrate is produced by the method including contacting a surface of a substrate having a coating of a solution of a first solvent and an organometallic halide thereon with a second solvent, wherein the organometallic halide is insoluble
 15 in the second solvent and the first solvent is miscible with the second solvent, wherein the first solvent is extracted from the coating of the solution into the second solvent, and wherein the organometallic halide precipitates from the solution onto the surface of the substrate forming an organometallic halide coating on the substrate. According to this aspect, various solvents
 20 organometallic halides, substrates and conditions described herein may be used.

The following examples are set forth as being representative of the present invention. These examples are not to be construed as limiting the scope of the invention as these and other equivalent embodiments will be apparent in view of the present disclosure, figures and accompanying claims.

25

EXAMPLE I

Deposition of Organometallic Halide Thin Films

All reagent grade chemicals are commercially obtained from Sigma-Aldrich (St. Louis, MO) unless noted otherwise.

30 Methylammonium iodide ($\text{CH}_3\text{NH}_3\text{I}$ or MAI) was prepared using a process as described in M. M. Lee, J. Teuscher, T. Miyasaya, T. N. Murakami, H.J. Snaith, *Science* 338, 643-647 (2012). In a typical procedure, 24 ml of 33 wt% methylamine (CH_3NH_2) solution in anhydrous ethanol was reacted with 10 ml of 57 wt% hydroiodic acid (HI) in water, in 100 ml of ethanol (excess CH_3NH_2) in a dry argon atmosphere at room temperature. The solvent and the excess CH_3NH_2 were
 35 removed using a rotary evaporator, and the resulting MAI powder was obtained. For preparation of $\text{CH}_3\text{NH}_3\text{Br}$ (MABr) the same procedure was followed except HI was replaced by HBr.

For typical preparation of MAPbI_3 perovskite films using the solven-solvent extraction (SSE) method, a solution of PbI_2 (Alfa-Aesar, Ward Hill, MA) and MAI from (molar ratio 1:1) in N-Methyl-2-pyrrolidone (NMP) was first spin-coated onto previously patterned fluorine-doped tin oxide (FTO) coated glass substrates (TEC 15, Hartford Glass Co., Hartford City, IN). The spin-coated substrate with the solution film was immersed in anhydrous diethyl ether (Fisher Scientific, Fair Lawn, NJ). After 2 min, a brown film was formed on the substrate. The substrate was taken out and dried rapidly in the ambient atmosphere due to the highly evaporative nature of the diethyl ether. The entire perovskite film fabrication process was performed in an ambient atmosphere with about 30% humidity. The thickness of the resultant perovskite film was controlled by varying the perovskite solution concentration and the spinning rate. Films of thickness 20 nm, 80 nm, 250 nm were processed using 15 wt%, 30 wt%, and 42 wt% solutions at 6000 rpm (10 s), 6000 rpm (10 s), and 4500 rpm (15 s), respectively. For the preparation of MAPbI_2Br , MAPbIBr_2 , and MAPbBr_3 , the starting precursors used were $\text{MABr:PbI}_2::1:1$, $\text{MAI:PbBr}_2::1:1$, and $\text{MAI:PbBr}_2::1:1$, respectively.

Fig. 1A is a schematic diagram depicting the solution-processing method described herein and referred to as “solvent-solvent extraction” or SSE wherein a co-solvent system is used to precipitate organometallic halides on the surface of a substrate. In the case of deposition of the hybrid perovskite MAPbI_3 , the first step involves room-temperature spin-coating of a solution of stoichiometric MAPbI_3 in NMP — a high-boiling-point (202 °C) polar solvent — on substrates. Other deposition methods, such as dip-coating, spraying, or inkjet-printing, can also be used to deposit the MAPbI_3 precursor solution. The clear spin-coated MAPbI_3 precursor thin film is immersed in a room-temperature bath of diethyl ether ($\text{C}_2\text{H}_5\text{OC}_2\text{H}_5$ or DEE) — a low-boiling-point non-polar solvent. Within seconds colored specks appear on the film, and it starts to turn dark uniformly, indicating the rapid formation of MAPbI_3 perovskite. Within two minutes NMP solvent extraction and simultaneous crystallization of the MAPbI_3 perovskite is complete. The substrate with the thin film of crystallized perovskite is then taken out from the bath and dried rapidly in ambient air.

Fig. 2A is a photograph of a substrate that has been spin-coated with a thin film of MAPbI_3 . Fig. 2B is a photograph of the substrate submerged or immersed in a vial of a volume of diethyl ether after 2 seconds showing MAPbI_3 coating formation indicated by the dark yellow or brownish color. Fig. 2C is a photograph of the substrate submerged or immersed in a vial of a volume of diethyl ether after 2 minutes showing MAPbI_3 coating formation indicated by the brownish color.

Fig. 3 is a sequence of photographs after submerging a spin-coated MAPbI_3 precursor thin film (patterned) in diethyl ether solvent showing rapid MAPbI_3 perovskite thin film formation. Fig. 4 is a sequence of photographs after adding drops of MAPbI_3 precursor solution (in NMP) in

diethyl ether bath showing sluggish MAPbI₃ perovskite precipitate formation compared to that in Fig. 3. This indicates that the thin film formation of the solution of the organometallic halide and the solvent is advantageous in the formation of a layer or coating or film of the crystallized organometallic halide on the surface of the substrate.

5

EXAMPLE II

Material Characterization

X-ray diffraction (XRD) was performed on a X-ray diffractometer (D-8 Discover, Bruker, Germany) using Cu K α ₁ radiation ($\lambda=1.5406$ Å) at a step size of 0.02°. XRD patterns for the confirmation of the perovskite phase were collected using a Ge (002) monochromator, at step time of 2 seconds. For XRD patterns for the tracking of the SSE process, the step time was 1 second, and the monochromator was not used.

The surface and cross-sections (fractured) morphology of thin films were characterized using a scanning electron microscope (SEM; LEO 1530VP, Carl Zeiss, Germany).

Transmission electron microscopy (TEM) was used to characterize cross-sections of the solar cell devices. Samples from specific locations on the cross-sections were prepared by focused ion beam (FIB; Helios 600, FEI, Hillsboro, OR) and *in situ* lift-out. In the case of plan-view high-resolution TEM, the SSE processed perovskite was deposited directly on a Cu grid covered with holey carbon (EMS, Hatfield, PA). The spin-coating conditions used were identical to those used to deposit 80 nm perovskite thin films. All TEM samples were examined using TEM (2100F, JEOL, Tokyo, Japan) operated at 200 kV accelerating voltage.

The optical spectroscopy (transmission, reflection and absorption) of SSE perovskite thin films on compact TiO₂-coated FTO were conducted at a step size of 10 nm on a Cary 6000i UV-vis-NIR spectrophotometer equipped with diffuse reflectance accessories (Agilent Technologies, Englewood, CO).

Atomic force microscopy (AFM) images were obtained in tapping mode (Veeco 5000 and Nanoscope V, Plainview, NY) using a probe with tip radius of about 10 nm and resonance frequency of about 300 kHz (Olympus AC160TS, Olympus, Japan). The AFM system is setup in an Ar glove box with H₂O and O₂ concentrations less than 0.1 ppm.

Figure 1B shows an indexed X-ray diffraction (XRD) pattern from an about 250 nm thick perovskite thin film deposited using the SSE method on a glass substrate, confirming pure - MAPbI₃ tetragonal phase (space group *I4/mcm*). Figures 1C and 1D are scanning electron microscope (SEM) images of a top surface of a typical SSE MAPbI₃ perovskite thin film (about 200 nm thickness), deposited on a fluorinated tin oxide (FTO) coated glass substrate with an about 20 nm TiO₂ hole-blocking layer, at low and high magnifications, respectively. The uniform, dense coverage is readily apparent from these micrographs, and the grain size is found to be about 200

nm.

Fig. 5A is a cross-sectional SEM image of an about 250 nm SSE MAPbI₃ perovskite thin film, showing uniform coverage and thickness. Cross-section of a thinner (about 80 nm) SSE MAPbI₃ perovskite thin film viewed in the transmission electron microscope (TEM; bright-field image) is presented in Fig. 5B, showing uniform, conformal coverage. Figs. 5C and 5D are high-resolution TEM images of MAPbI₃ perovskite deposited on TEM grids using the SSE method. The about 8.8 Å interplanar spacing in Fig. 5D corresponds to (100) or (010) planes (lattice parameters $a=b=8.849$ Å, $c=12.642$ Å (See C. C. Stoumpos, C. D. Malliakas, M. G. Kanatzidis, *Inorg. Chem.* 52, 9019-9038 (2013)), further confirming the -MAPbI₃ tetragonal phase. Proliferation of crystal defects are also observed in Fig. 5C, which is typical of soft organic-inorganic hybrid materials. The atomic force microscope (AFM) images in Fig. 5E (40×40 μm²) and Fig. 5F (2×2 μm²) of the top surface of a SSE MAPbI₃ perovskite thin film (thickness about 250 nm) reveal root mean square (RMS) roughness of about 4.0 nm and about 5.2 nm, respectively, showing unprecedented smoothness over a large area. The highly reflective nature of the film is shown in the photograph in Fig. 5H, and the photograph in Fig. 5G demonstrates the semitransparent nature of the SSE MAPbI₃ perovskite thin film (thickness about 350 nm) over a 5×6 cm² area viewed in bright sunshine.

Fig. 6A-6D are cross-sectional SEM images of MAPbI₃ perovskite films of various thicknesses deposited on TiO₂-blocking-layer coated FTO-glass substrates using the SSE process at room temperature, and the corresponding photographs demonstrating semitransparency: Fig. 6A is about 50 nm, Fig. 6B is about 80 nm, Fig. 6C is about 250 nm, and Fig. 6D is about 410 nm. Fig. 7 is a cross-sectional bright-field TEM image of an about 20 nm MAPbI₃ perovskite film deposited on TiO₂-blocking-layer coated FTO-glass substrates. Fig. 8A-8D are bright field TEM images of a typical MAPbI₃ perovskite-based solar cell device, where the MAPbI₃ thin film (about 700 nm thickness) is deposited using the SSE process at room temperature: Fig. 8A is an overall view. Fig. 8B is a detailed view of region "B" showing hole-transporting material (HTM) and MAPbI₃. Fig. 8C is a detailed view of region "C" showing MAPbI₃ grains, and Fig. 8D is a detailed view of region "D" showing MAPbI₃, TiO₂ blocking layer and FTO. The thickness of the MAPbI₃ layer in this solar cell is unusually thick, and Au was used as the top contact instead of Ag used in other cells. Fig. 9 depicts images of elemental EDS mapping of the solar cell device in Fig. 7 showing the distribution of elements Sn, Ti, Pb, I, and Au. Fig. 10A-10C depict optical properties of MAPbI₃ perovskite films of various thicknesses deposited on TiO₂-blocking-layer coated FTO-glass substrates using the SSE process at room temperature: Fig. 10A shows transmission. Fig. 10B shows reflection. Fig. 10C shows absorption. Inset in Fig. 10B are photographs of the films.

Figs. 11A-11C are X-ray diffraction (XRD) patterns following the progression of the SSE

deposition process on a glass substrate. Fig. 11A shows featureless XRD pattern from the as-spin-coated MAPbI₃ precursor solution thin film, while Fig. 11B shows the formation of MAPbI₃ perovskite after 2 seconds of NMP-solvent extraction. Upon further NMP extraction (2 minutes), the XRD pattern become sharper, where the strongest reflection in Fig. 11C is narrower (FWHM

5 2 0.31°) compared to that in Fig. 11B (FWHM 2 ~0.61°), showing the formation of phase-pure β-MAPbI₃ perovskite (film thickness about 250 nm). Fourier-transform infrared (FTIR) spectra from the films corresponding to Fig. 11B (2 seconds) and Fig. 11C (2 min) are presented in Fig. 11D. The presence of C=O stretching band at about 1700 cm⁻¹ observed in the 2 second spectrum (red) is indicative of the presence of some NMP remaining in the thin film, but it

10 disappears in the fully solvent-extracted thin film at 2 minutes (black). Based on these observations it appears that as soon as the MAPbI₃ precursor film comes in contact with DEE, the NMP solvent is extracted selectively as NMP is highly miscible in DEE. This may occur in localized patches in the very early stages which can be due to local compositional variations in the film and/or the DEE solvent in contact with the film. The crystallization of MAPbI₃ perovskite is

15 triggered in areas devoid of NMP, which spreads rapidly to cover the entire area as all the NMP is extracted by DEE. The process of extracting the NMP solvent by the DEE solvent and deposition of organometallic halide crystals is schematically depicted in Fig. 11E. Since MAPbI₃ perovskite is insoluble in non-polar DEE and the process is so rapid, the crystallized film is not damaged during this room-temperature process. Finally, the lower boiling point of DEE (35 °C), compared

20 to the precursor solvents (NMP 204 °C), allows ambient drying to remove any remaining DEE solvent.

While the NMP/DEE precursor/extracting solvents combination used here is a typical example for the demonstration of the SSE method, a wide range of other solvents, or mixed solvents, can be used to suit the specific perovskite being deposited. According to certain aspects,

25 an exemplary precursor solvent (polar) has a high solubility for perovskite precursor, allows deposition of films with wide range of uniform thicknesses, and a high boiling point, preventing evaporation-induced unbalanced perovskite growth and/or the possible formation of complexes. An exemplary extracting solvent (non-polar) has no or substantially no solubility for the perovskite precursors, it does not react with the solid perovskites, and it has a low boiling point, allowing

30 rapid drying in ambient conditions. An exemplary precursor solvent is highly miscible in the extracting solvent, and it disperses rapidly, enabling rapid SSE deposition.

EXAMPLE III

Solar Cell Fabrication and Testing

35 For the fabrication of the solar cells, FTO-coated glass was patterned by hydrochloric acid etching with zinc powder, and cleaned by soaking in a base bath (5 wt % NaOH in ethanol)

overnight. After washing using deionized water and ethanol, a compact TiO₂ layer was deposited on top of patterned FTO by spray pyrolysis at 450°C. The perovskite layer was then deposited as described above in Example I. This was followed by spin-coating a solution of hole transporting materials (HTMs), which included 80 mg 2,2',7,7'-tetrakis(N,N-dip-methoxyphenylamine)-9,9'-
 5 spirobifluorene (Spiro-MeOTAD; Merck, Germany), 30 μ l bis(trifluoromethane)sulfonimide lithium salt stocking solution (500 mg Li-TFSI in 1 ml acetonitrile), and 30 μ l 4-tert-butylpyridine (TBP), and 1 ml chlorobenzene solvent. Finally a 150 nm Ag layer was deposited using a thermal evaporator and a shadow mask. The cells were stored in a dry-air atmosphere with humidity below 10%, and typically the performance of the solar cell was measured one day after fabrication.

10 The incident photon-to-current efficiency (IPCE) or external quantum efficiency spectra were recorded at a chopping frequency of 5 Hz in AC mode on a solar cell quantum efficiency measurement system (QEX10, PV Measurements, Boulder, CO). The *J-V* characteristics of the cells were obtained using a 2400 SourceMeter (Keithley, Cleveland, OH) under simulated one sun AM 1.5G illumination, 100 mW.cm⁻² (Oriel Sol3A class AAA Solar Simulator, Newport
 15 Corporation, Irvine, CA). Typical sweeping of forward bias voltage started from 0 V to *V*_{oc} + 50 mV and back to 0 V, at the rate of 20 mV s⁻¹. A typical active area of 0.16 cm² was defined using a non-reflective mask for the *J-V* measurements. Using a procedure suggested by H. J. Snaith, *J. Phys. Chem. Lett.* 4, 3623-3630 (2013), the maximum power output stability of the solar cells was measured by monitoring the current density (*J*) output at the maximum power voltage (*V*) bias for
 20 up to 300 seconds using a VersaSTAT MC potentiostat (Princeton Applied Research, Acton, MA). The current output can be converted to PCE output using the following relation: PCE = [*J* (mA.cm⁻²) × *V* (V)]/[100 (mW.cm⁻²)]. A shutter used to control the one-sun illumination on the cell. The stabilizing output PCEs at maximum power point of the SSE perovskite solar cells is close to the calculated PCEs from the reverse scan *J-V* response at the measurement conditions described
 25 above. The cell testing was conducted in an ambient atmosphere with humidity of 20-40%. Impedance spectroscopy (IS) on the solar cells was performed using a PARSTAT 2273 workstation (Princeton Applied Research, Acton, MA) with the frequency range of 0.1 Hz–100 kHz and the modulation amplitude of 10 mV. The IS spectra were analyzed using ZView 2.9c software (Scribner Associates, Southern Pines, NC).

30 Fig. 12A presents typical current density (*J*) - voltage (*V*) curves under simulated one-sun AM 1.5G (100 mW.cm⁻²) illumination of solar cells fabricated using SSE MAPbI₃ perovskite thin films of thickness about 20 nm, about 80 nm, and about 250 nm. The solar-cell performance parameters extracted from these data are presented in Table 1 below with * representing the solar cell with highest PCE.

SSE Perovskite Thickness	J_{sc} (mA.cm ⁻²)	FF	V_{oc} (V)	PCE (%)
20 nm	7.3	0.638	0.88	4.1
80 nm	14.1	0.663	1.08	10.1
250 nm	19.0	0.659	1.07	13.4
250 nm*	20.7	0.680	1.08	15.2

When the perovskite film thickness is about 20 nm, the solar cell exhibits a PCE of 4.1% with a short-circuit photocurrent density (J_{sc}) of 7.3 mA.cm⁻², open-circuit voltage (V_{oc}) of 0.88 V, and fill factor (FF) of 0.638. The device PCE increases to 10.1% and 13.4% when the perovskite film thickness is increased to about 80 and about 250 nm, respectively. The highest PCE observed is 15.2% for a solar cell with about 250 nm perovskite film thickness. The improved efficiency with increasing perovskite film thickness is mainly the result of the larger J_{sc} values associated with the increased optical absorption. The J_{sc} values for these perovskite cells are consistent with their respective external quantum efficiency (EQE) spectra which are shown in Fig. 12B. To verify the PCE values determined from the J - V characteristics, the stable, maximum power output under continuous one-sun illumination is measured. Figure 13 shows that for a typical solar cell made using about 250 nm SSE MAPbI₃ perovskite thin film, the maximum power output stabilizes at about 13.2% over several minutes, which compares favorably with the values obtained from the J - V curve (13.4%; Fig. 12A). Fig. 13 depicts stability of current density (J) and PCE (η) as a function of time for a solar cell device based on MAPbI₃ perovskite thin film (about 250 nm thickness) under simulated one-sun AM 1.5G (100 mW/m²) illumination (0.16 cm² active area).

The mean, maximum, and minimum PCE values for 10-20 solar cells tested for each perovskite thickness are presented in Fig. 14. The tight distribution of PCE values indicates that the SSE method for MAPbI₃ perovskite thin film deposition is reproducible. While the highest PCE of 15.2% is for cells based on about 250-nm thickness films, PCE of over 10% for solar cells made from an about 80-nm thick MAPbI₃ perovskite film were achieved. When the film thickness is reduced down to about 20 nm, an average PCE of 4.1% is achieved.

Impedance analyses show that the smaller recombination resistance for the 20 nm solar cell accounts for the observed lower V_{oc} compared to the 80–250-nm solar cells. Impedance spectroscopy was used to investigate the effect of perovskite film thickness on the recombination resistance (R_{recomb}) for perovskite solar cells based on MAPbI₃ thin films prepared with the SSE method. Figure 15A shows a typical Nyquist plot of impedance spectra in the complex plane for a 250-nm perovskite cell under three different bias voltages. The impedance spectra for all three bias voltages are dominated by a large semicircle at low frequencies. This large semicircle is often

attributed to the charge recombination process within the perovskite solar cells. The model used for impedance analysis has been previously discussed in detail (see J. A. Christians, et al., *J. Am. Chem. Soc.* 136, 758-764 (2014); H.-S. Kim, et al., *Sci. Rep.* 2, 591 (2012); E. J. Juarez-Perez, et al., *J Phys. Chem. Lett.* 5, 680-685 (2014).) Figure 15B compares the recombination resistance R_{Recomb} as a function of voltage for MAPbI₃ perovskite solar cells with three different film thicknesses. The R_{Recomb} for all three samples depends strongly on the bias voltage, following a similar voltage dependence. When compared at a fixed voltage, the R_{Recomb} values for the 20-nm sample are significantly (about a factor of 5–10) smaller than the cells with 80–250 nm thick perovskite layers. A smaller R_{Recomb} corresponds to a faster recombination rate, which could account for the observed lower V_{oc} for the 20-nm film solar cell compared to that for the 80–250-nm film solar cells.

EXAMPLE IV

Thickness and Composition Control of Perovskite Thin Coatings

The methods described herein are highly versatile and can be used to deposit semitransparent thin films or coatings of MAPbI_(3-x)Br_x ($x = 1, 2, \text{ or } 3$) perovskites with vivid colors, which can be tuned via thickness and composition (I/Br ratio) control. Figs. 16A-16D show XRD patterns from MAPbI_(3-x)Br_x perovskite films deposited on glass substrates using the SSE process at room temperature: Fig. 16A $x=0$, Fig. 16B $x=1$, Fig. 16C $x=2$, and Fig. 16D $x=3$. The peak shift due to change in the lattice parameters is denoted by the dashed red lines and the arrows. Fig. 17 show photographs of MAPbI_(3-x)Br_x perovskite films deposited on TiO₂-blocking-layer coated FTO-glass substrates using the SSE process at room temperature as a function of I/Br ratio 0 to 3 and thickness in the range about 20 nm to about 250 nm, demonstrating that the semitransparency and color can be tuned through these variables.

Typical solar cells based on about 80-nm thick SEE MAPbI₂Br films (1.8 eV band gap (see Y. Zhao, K. Zhu, *J. Am. Chem. Soc.* 136, 12241-12244 (2014)) deliver a promising PCE of 8.3% as per Fig. 18 which shows J-V characteristics and extracted performance parameters for a solar cell device based on MAPbI₂Br perovskite thin film (~80 nm thickness) under simulated one sun AM 1.5G (100 mW/m²) illumination (0.16 cm² active area). The high PCEs in semitransparent, colorful solar cells with low lead content is advantageous for large-scale architectural applications such as decorative panels and windows. Also, the room-temperature nature of the solvent-solvent extraction process makes it highly compatible with the fabrication of tandem-architecture solar cells and continuous roll-to-roll manufacturing.

It is to be understood that the embodiments of the present invention which have been described are merely illustrative of some of the applications of the principles of the present invention. Numerous modifications may be made by those skilled in the art based upon the

teachings presented herein without departing from the true spirit and scope of the invention. The contents of all references, patents and published patent applications cited throughout this application are hereby incorporated by reference in their entirety for all purposes.

What is claimed is:

1. A method of making a coated substrate comprising
 contacting a surface of a substrate having a coating of a solution of a first solvent and an organometallic halide thereon with a second solvent,
 5 wherein the organometallic halide is insoluble in the second solvent and the first solvent is miscible with the second solvent,
 wherein the first solvent is extracted from the coating of the solution into the second solvent, and
 wherein the organometallic halide precipitates from the solution onto the surface of the
 10 substrate forming an organometallic halide coating on the substrate.
2. The method of claim 1 wherein the coating of the solution is formed by applying the solution to the surface of the substrate and removing a portion of the first solvent.
- 15 3. The method of claim 1 wherein the organometallic halide is RMe_nX_y wherein Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb; X is one or more of I, Br, Cl; y is 3 or $(3n+1)$; n is 1, 2, 3, 4, 5; R is an organic group, CH_3NH_3 , $\text{NH}_3\text{CH}=\text{CH}_2$, Cs, $(\text{R}'\text{-NH}_3)_2$, $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ or $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$; and R' is alkyl, C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$; with the proviso that when y is 3, n is 1, Me is Pb, Sn, Ge, Eu or Yb and R is an organic group, CH_3NH_3 or $\text{NH}_3\text{CH}=\text{CH}_2$, or Cs, and further
 20 with the proviso that when y is $(3n+1)$ and n is 1, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb, and R is $(\text{R}'\text{-NH}_3)_2$ or $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ and further with the proviso that when y is $(3n+1)$ and n is 2, 3, 4, or 5, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb and R is $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$.
4. The method of claim 1 wherein the organometallic halide is RMeX_3 wherein R is an
 25 organic group or Cs, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of I, Br, Cl.
5. The method of claim 1 wherein the organometallic halide is RMeX_3 wherein R is Cs or an organic group selected from the group consisting of CH_3NH_3 or $\text{NH}_2\text{CH}=\text{CH}_2$, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of Cl, Br, or I.
 30
6. The method of claim 1 wherein the organometallic halide is $\text{CH}_3\text{NH}_3\text{PbI}_3$.
7. The method of claim 1 wherein the organometallic halide is $(\text{R-NH}_3)_2\text{MeX}_4$ wherein R is alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is a transition metal or a rare earth metal and X is one or more of Cl, Br, or
 35 I.

8. The method of claim 1 wherein the organometallic halide is $(R-NH_3)_2MeX_4$ wherein R is C_1 to C_4 alkyl or $C_6H_5C_2H_4$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.
- 5 9. The method of claim 1 wherein the organometallic halide is $(NH_3-R-NH_3)_2MeX_4$ wherein R is alkyl or $C_6H_5C_2H_4$, Me is a transition metal or a rare earth metal and X is one or more of Cl, Br, or I.
- 10 10. The method of claim 1 wherein the organometallic halide is $(NH_3-R-NH_3)_2MeX_4$ wherein R is C_1 to C_4 alkyl or $C_6H_5C_2H_3$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.
11. The method of claim 1 wherein the organometallic halide is $(R'NH_3)_2(R)_{(n-1)}Me_nX_{(3n+1)}$ wherein R' is C_1 to C_4 alkyl or $C_6H_5C_2H_4$, R is Cs, CH_3NH_3 or $NH_2CH=CH_2$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb, X is one or more of Cl, Br, or I and n is 2, 3, 4, or 5.
- 15 12. The method of claim 1 wherein the first solvent is a polar solvent having a boiling point within the range of 100 °C and 300 °C.
- 20 13. The method of claim 1 wherein the first solvent is dimethylformamide, dimethylsulfoxide, γ -butyrolactone, n-methyl-2-pyrrolidone, dimethylacetamide or dimethylphosphoramidate.
14. The method of claim 1 wherein the second solvent is a nonpolar solvent having a boiling point within the range of 0 °C and 100 °C.
- 25 15. The method of claim 1 wherein the second solvent is diethyl ether, pentane, cyclopentane, hexane, cyclohexane, benzene, chloroform, carbon disulphide, carbon tetrachloride, dibutyl ether, diethylamine, trichloroethylene, triethylamine or dichloromethane.
- 30 16. The method of claim 1 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature between 10 °C and below 70 °C.
- 35 17. The method of claim 1 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature between 10 °C and 50 °C.

18. The method of claim 1 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature of between 20 °C and 30 °C.
- 5 19. The method of claim 1 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature of between 18 °C and 23 °C.
- 10 20. The method of claim 1 wherein the coating has a thickness of between 20 nm and 2 μm.
21. The method of claim 1 wherein the substrate surface includes one or more of a polymer, glass, ceramic, or metal.
- 15 22. The method of claim 1 wherein the second solvent extracts the first solvent forming a miscible mixture of the second solvent and the first solvent and the organometallic halide crystallizes from solution onto the surface of the substrate.
23. The method of claim 1 wherein the solution is applied to the substrate by spin coating, dip
20 coating, spray coating, or ink jet printing.
24. The method of claim 1 wherein the first solvent and the second solvent is removed from the coated substrate.
- 25 25. The method of claim 1 wherein the coated substrate is dried at a temperature of between 18°C and 100°C.
26. The method of claim 1 wherein the coating has an average uniform surface roughness of between about 1 nm and 20 nm (root mean square) as measured using an atomic force microscope.
- 30 27. The method of claim 1 wherein applying the second solvent to the surface of the substrate and contacting the solution is carried out by immersing the substrate in the second solvent.
28. A solar cell including a coated substrate wherein the coating is a room temperature co-
35 solvent precipitate of an organometallic halide.

29. The solar cell of claim 28 wherein the organometallic halide is RMe_nX_y wherein Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb; X is one or more of I, Br, Cl; y is 3 or $(3n+1)$; n is 1, 2, 3, 4, 5; R is an organic group, CH_3NH_3 , $\text{NH}_3\text{CH}=\text{CH}_2$, Cs, $(\text{R}'\text{-NH}_3)_2$, $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ or $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$; and R' is alkyl, C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$; with the proviso that when y is 3, n is 1, Me is Pb, Sn, Ge, Eu or Yb and R is an organic group, CH_3NH_3 or $\text{NH}_3\text{CH}=\text{CH}_2$, or Cs, and further with the proviso that when y is $(3n+1)$ and n is 1, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb, and R is $(\text{R}'\text{-NH}_3)_2$ or $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ and further with the proviso that when y is $(3n+1)$ and n is 2, 3, 4, or 5, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb and R is $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$.
30. The solar cell of claim 28 wherein the organometallic halide is RMeX_3 wherein R is Cs, CH_3NH_3 or $\text{NH}_2\text{CH}=\text{CH}_2$, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of Cl, Br, or I.
31. The solar cell of claim 28 wherein the organometallic halide is $(\text{R-NH}_3)_2\text{MeX}_4$ wherein R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.
32. The solar cell of claim 28 wherein the organometallic halide is $(\text{NH}_3\text{-R-NH}_3)_2\text{MeX}_4$ wherein R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_3$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.
33. The solar cell of claim 28 wherein the organometallic halide is $(\text{R}'\text{NH}_3)_2(\text{R})_{(n-1)}\text{Me}_n\text{X}_{(3n+1)}$ wherein R' is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, R is Cs, CH_3NH_3 or $\text{NH}_2\text{CH}=\text{CH}_2$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb, X is one or more of Cl, Br, or I and n is 2, 3, 4, or 5.
34. A coated substrate produced by the method comprising
 contacting a surface of a substrate having a coating of a solution of a first solvent and an organometallic halide thereon with a second solvent,
 wherein the organometallic halide is insoluble in the second solvent and the first solvent is miscible with the second solvent,
 wherein the first solvent is extracted from the coating of the solution into the second solvent, and
 wherein the organometallic halide precipitates from the solution onto the surface of the substrate forming an organometallic halide coating on the substrate.
35. The coated substrate of claim 34 wherein the organometallic halide is RMe_nX_y wherein Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb; X is one or more of I, Br, Cl; y is 3 or $(3n+1)$;

n is 1, 2, 3, 4, 5; R is an organic group, CH_3NH_3 , $\text{NH}_3\text{CH}=\text{CH}_2$, Cs, $(\text{R}'\text{-NH}_3)_2$, $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ or $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$; and R' is alkyl, C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$; with the proviso that when y is 3, n is 1, Me is Pb, Sn, Ge, Eu or Yb and R is an organic group, CH_3NH_3 or $\text{NH}_3\text{CH}=\text{CH}_2$, or Cs, and further with the proviso that when y is $(3n+1)$ and n is 1, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb, and R is $(\text{R}'\text{-NH}_3)_2$ or $(\text{NH}_3\text{-R}'\text{-NH}_3)_2$ and further with the proviso that when y is $(3n+1)$ and n is 2, 3, 4, or 5, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Ge, Eu or Yb and R is $(\text{R}'\text{-NH}_3)_2\text{R}_{(n-1)}$.

36. The coated substrate of claim 34 wherein the coating of the solution is formed by applying the solution to the surface of the substrate and removing a portion of the first solvent.

37. The coated substrate of claim 34 wherein the organometallic halide is RMeX_3 wherein R is an organic group or Cs, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of I, Br, Cl.

38. The coated substrate of claim 34 wherein the organometallic halide is RMeX_3 wherein R is Cs or an organic group selected from the group consisting of CH_3NH_3 or $\text{NH}_2\text{CH}=\text{CH}_2$, Me is Pb, Sn, Ge, Eu or Yb and X is one or more of Cl, Br, or I.

39. The coated substrate of claim 34 wherein the organometallic halide is $\text{CH}_3\text{NH}_3\text{PbI}_3$.

40. The coated substrate of claim 34 wherein the organometallic halide is $(\text{R-NH}_3)_2\text{MeX}_4$ wherein R is alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is a transition metal or a rare earth metal and X is one or more of Cl, Br, or I.

41. The coated substrate of claim 34 wherein the organometallic halide is $(\text{R-NH}_3)_2\text{MeX}_4$ wherein R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb and X is one or more of Cl, Br, or I.

42. The coated substrate of claim 34 wherein the organometallic halide is $(\text{NH}_3\text{-R-NH}_3)_2\text{MeX}_4$ wherein R is alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_4$, Me is a transition metal or a rare earth metal and X is one or more of Cl, Br, or I.

43. The coated substrate of claim 34 wherein the organometallic halide is $(\text{NH}_3\text{-R-NH}_3)_2\text{MeX}_4$ wherein R is C_1 to C_4 alkyl or $\text{C}_6\text{H}_5\text{C}_2\text{H}_3$, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb Eu or Yb and X is one or more of Cl, Br, or I.

44. The coated substrate of claim 34 wherein the organometallic halide is $(R'NH_3)_2(R)_{(n-1)}Me_nX_{(3n+1)}$ wherein R' is C₁ to C₄ alkyl or C₆H₅C₂H₄, R is Cs, CH₃NH₃ or NH₂CH=CH₂, Me is Cu, Co, Ni, Fe, Mn, Pd, Cd, Sn, Pb, Eu or Yb, X is one or more of Cl, Br, or I and n is 2, 3, 4, or 5.
- 5 45. The coated substrate of claim 34 wherein the first solvent is a polar solvent having a boiling point within the range of 100 °C and 300 °C.
46. The coated substrate of claim 34 wherein the first solvent is dimethylformamide, dimethylsulfoxide, γ-butyrolactone, n-methyl-2-pyrrolidone, dimethylacetamide or
10 dimethylphosphoramidate.
47. The coated substrate of claim 34 wherein the second solvent is a nonpolar solvent having a boiling point within the range of 0 °C and 100 °C.
- 15 48. The coated substrate of claim 34 wherein the second solvent is diethyl ether, pentane, cyclopentane, hexane, cyclohexane, benzene, chloroform, carbon disulphide, carbon tetrachloride, dibutyl ether, diethylamine, trichloroethylene, triethylamine or dichloromethane.
49. The coated substrate of claim 34 wherein the organometallic halide precipitating onto the
20 surface of the substrate forming a coating and the coated substrate is carried out at a temperature between 10 °C and below 70 °C.
50. The coated substrate of claim 34 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature
25 between 10 °C and 50 °C.
51. The coated substrate of claim 34 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature of
30 between 20 °C and 30 °C.
52. The coated substrate of claim 34 wherein the organometallic halide precipitating onto the surface of the substrate forming a coating and the coated substrate is carried out at a temperature of
between 18 °C and 23 °C.
- 35 53. The coated substrate of claim 34 wherein the coating has a thickness of between 20 nm and 2 μm.

54. The coated substrate of claim 34 wherein the substrate surface includes one or more of a polymer, glass, ceramic, or metal.
- 5 55. The coated substrate of claim 34 wherein the second solvent extracts the first solvent forming a miscible mixture of the second solvent and the first solvent and the organometallic halide crystallizes from solution onto the surface of the substrate.
56. The coated substrate of claim 34 wherein the solution is applied to the substrate by spin
10 coating, dip coating, spray coating, or ink jet printing.
57. The coated substrate of claim 34 wherein the first solvent and the second solvent is removed from the coated substrate.
- 15 58. The coated substrate of claim 34 wherein the coated substrate is dried at a temperature of between between 18°C and 100°C.
59. The coated substrate of claim 34 wherein the coating has an average uniform surface roughness of between about 1 nm and 20 nm (root mean square) as measured using an atomic force
20 microscope.
60. The coated substrate of claim 34 wherein applying the second solvent to the surface of the substrate and contacting the solution is carried out by immersing the substrate in the second solvent.
- 25

Figure 1A

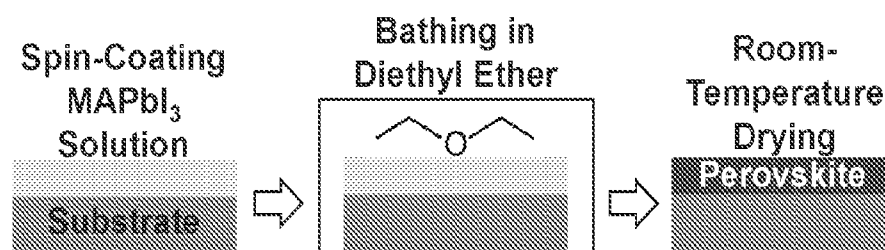


Figure 1B

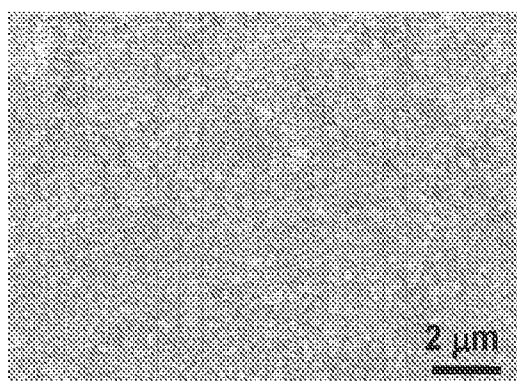
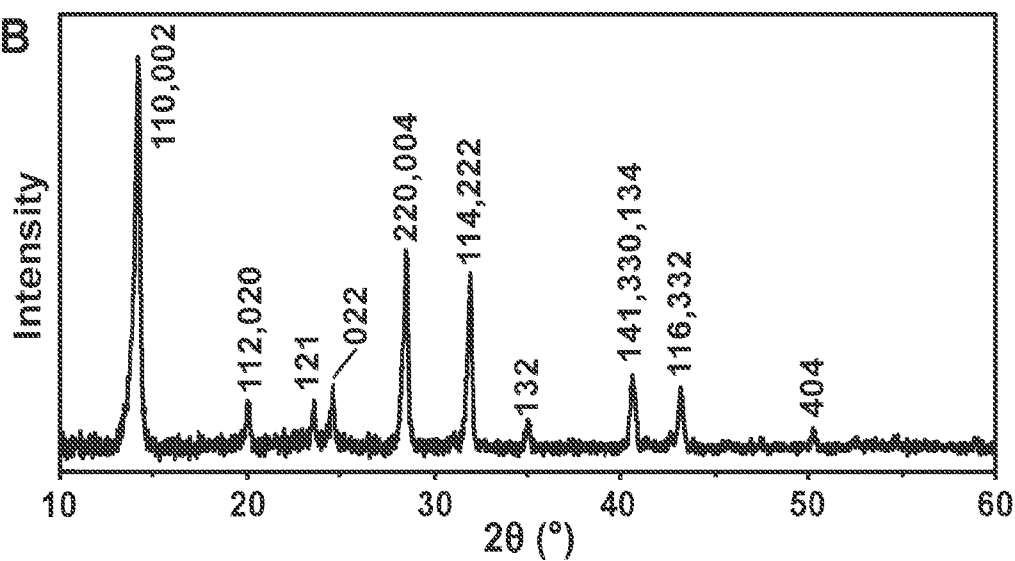


Figure 1C

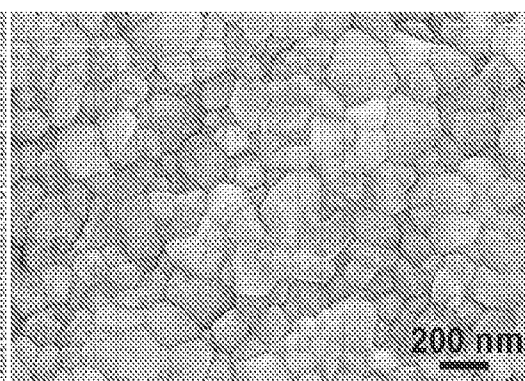


Figure 1D

Figure 2A

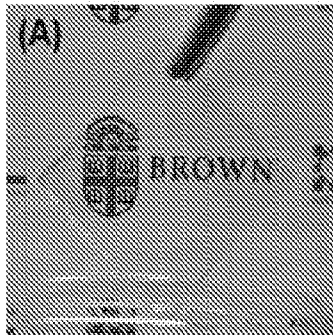


Figure 2B

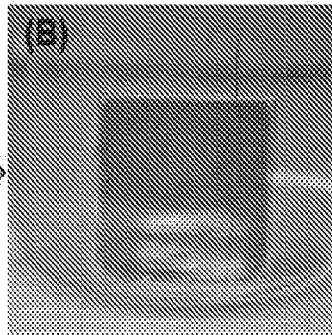


Figure 2C

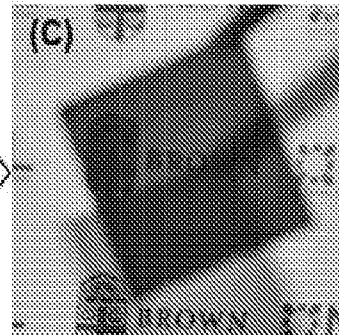


Figure 3

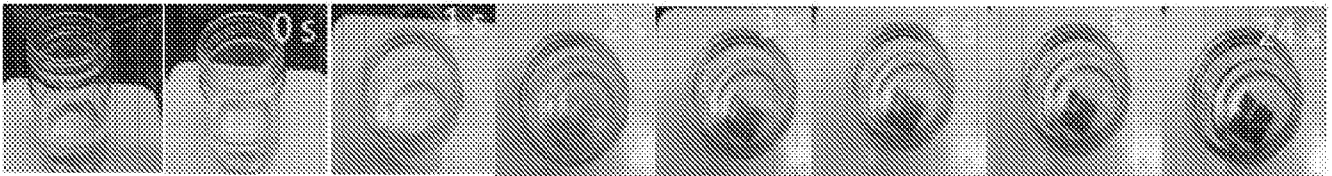
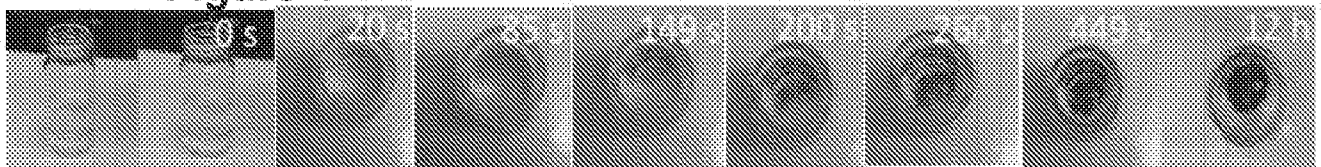


Figure 4



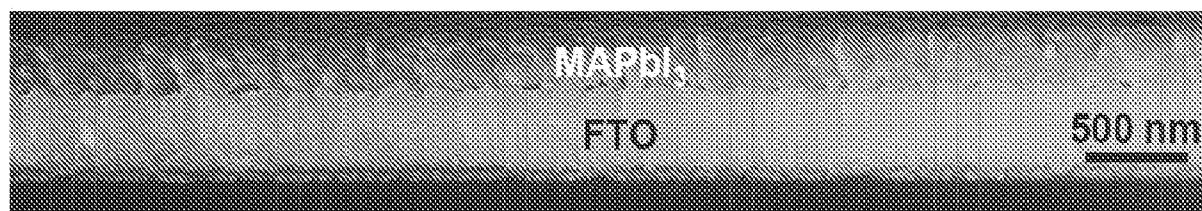


Figure 5B

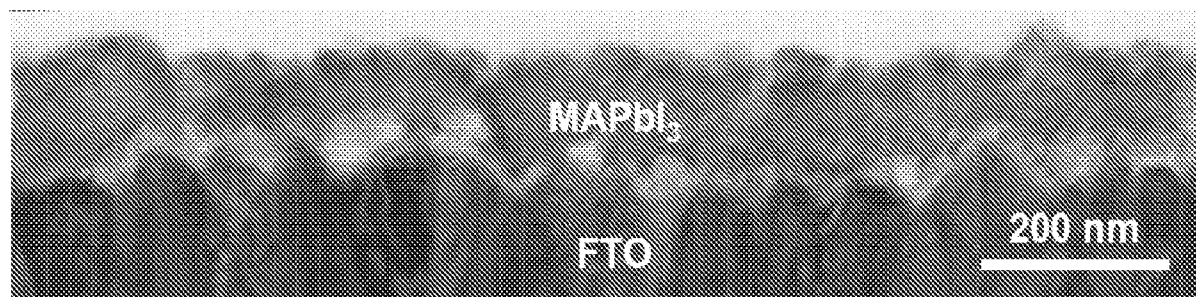


Figure 5C

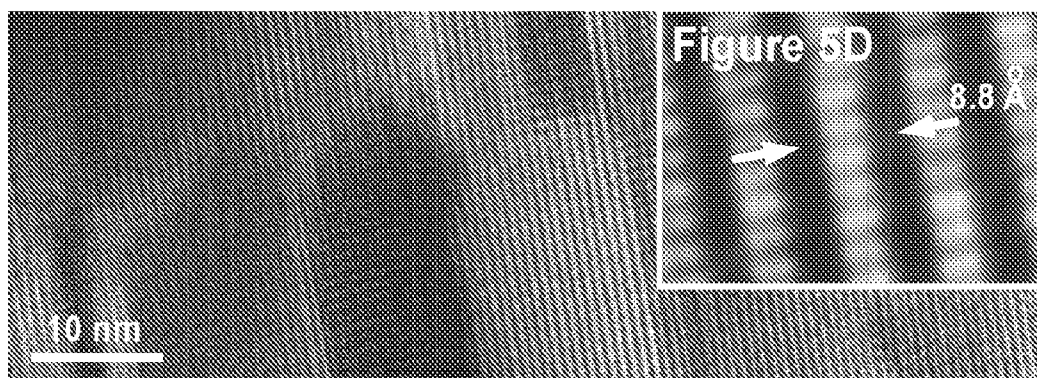


Figure 5E

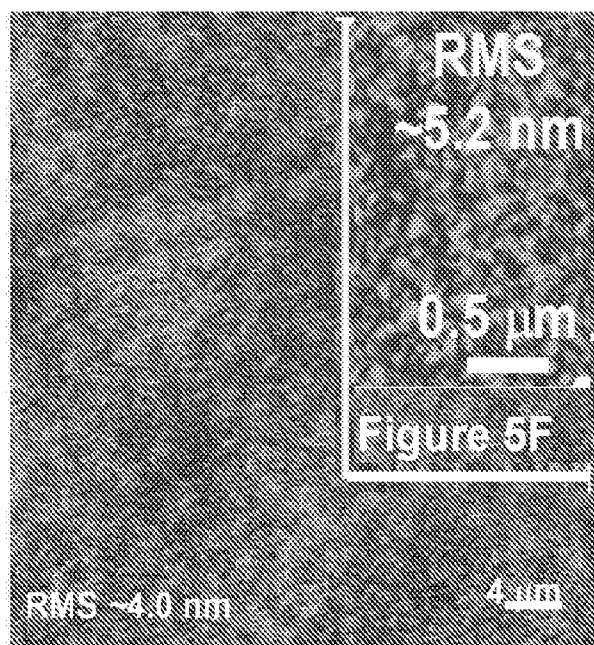


Figure 5H

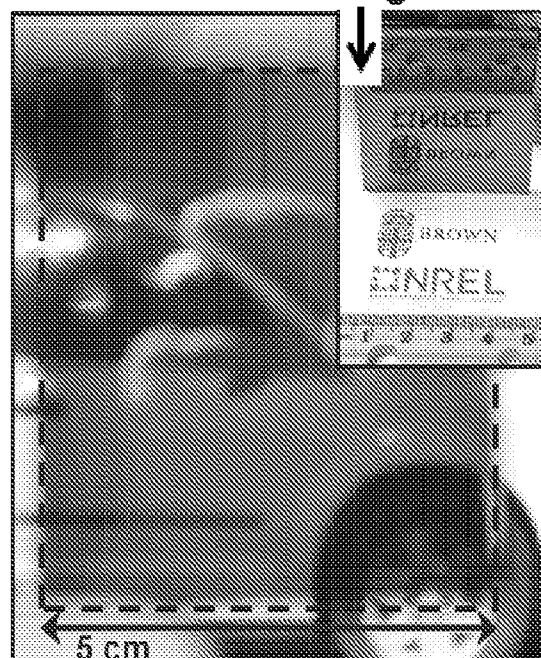


Figure 5G

Figure 6A

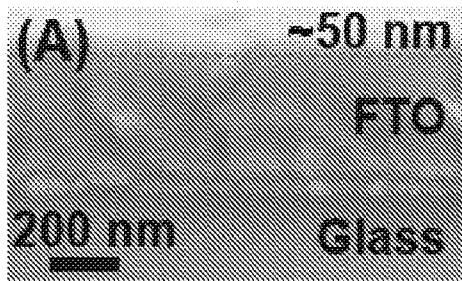


Figure 6B

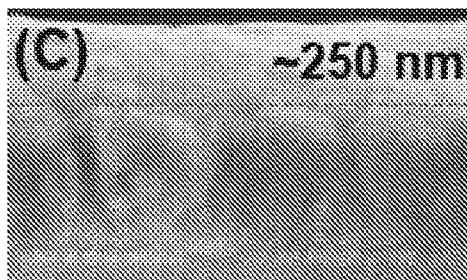
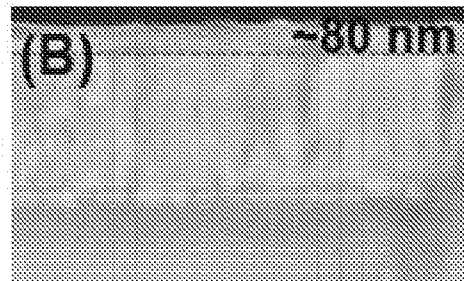


Figure 6C

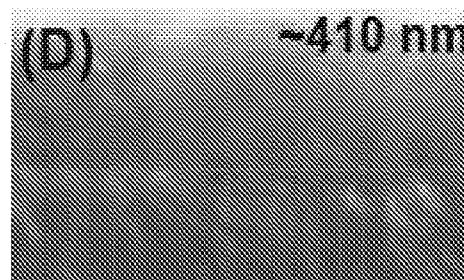


Figure 6D

Figure 7

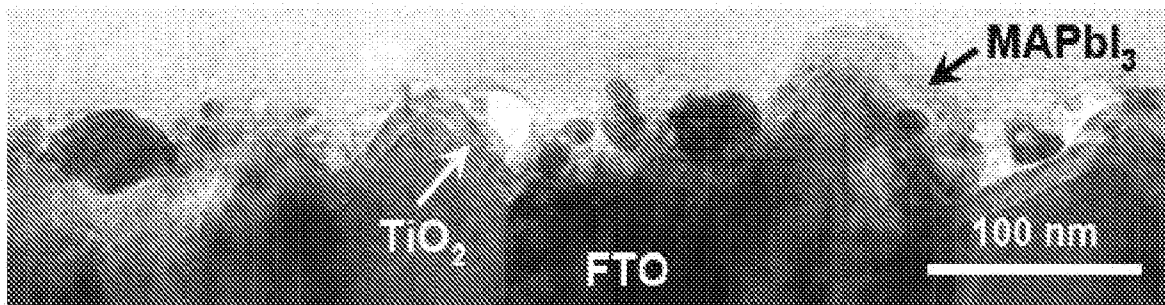


Figure 8A

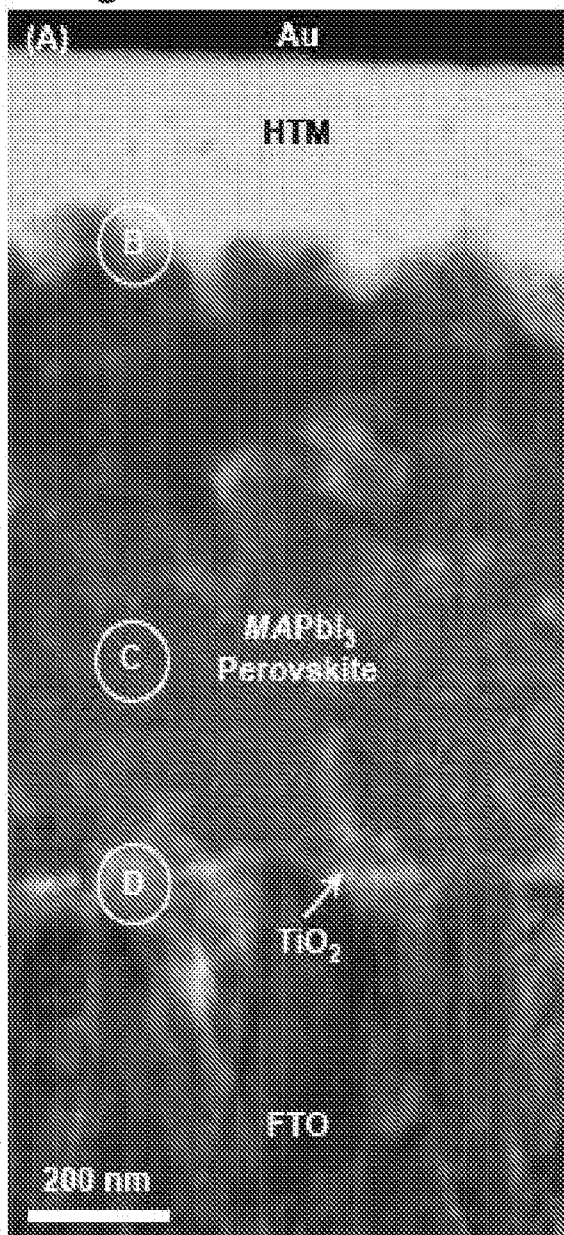


Figure 8B

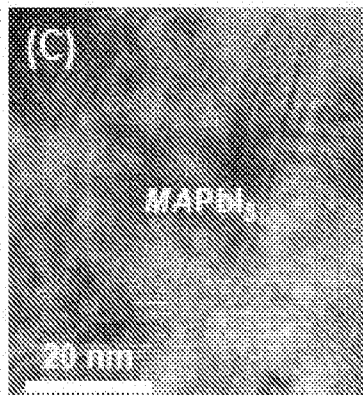
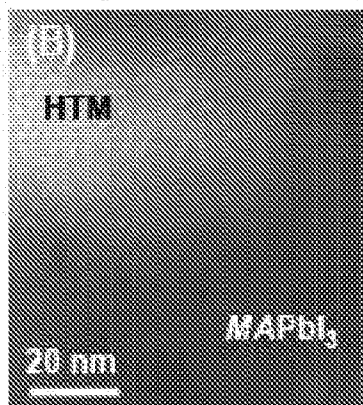


Figure 8C

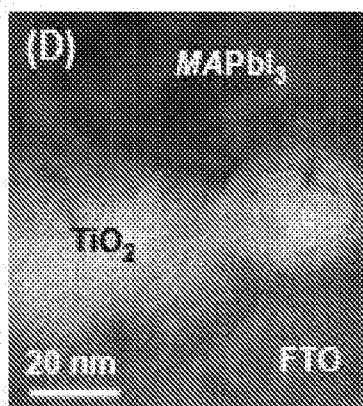


Figure 8D

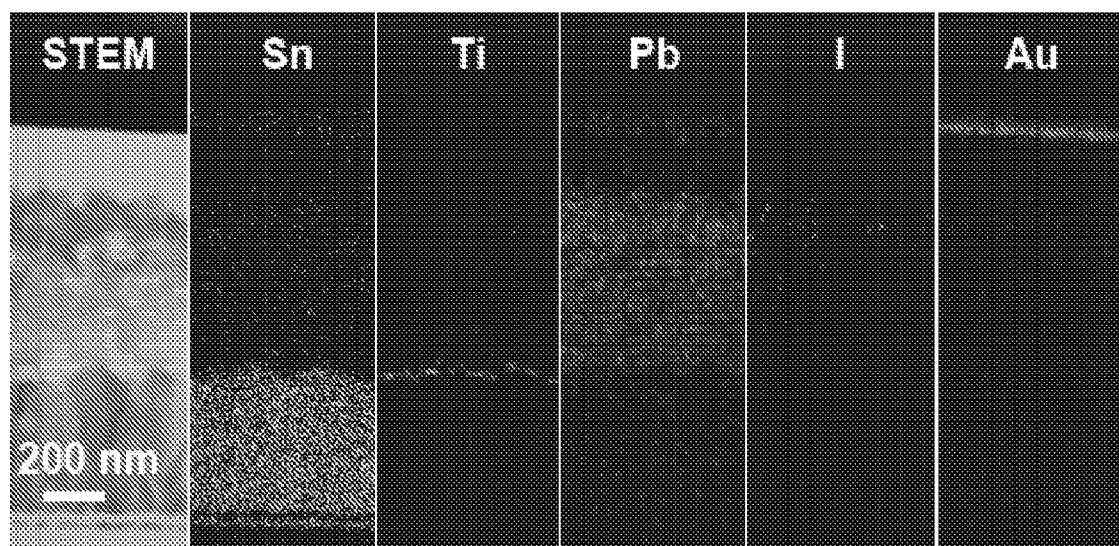


Figure 9

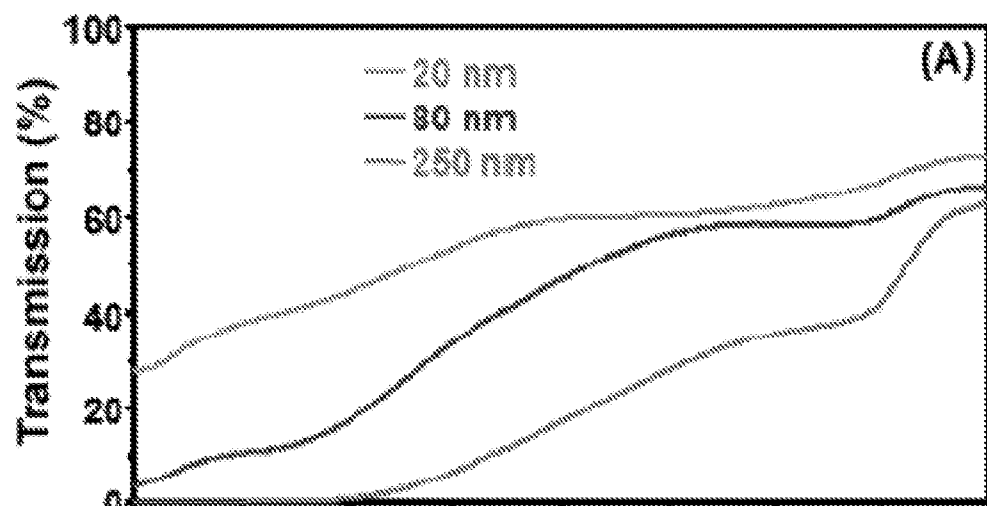


Figure 10A

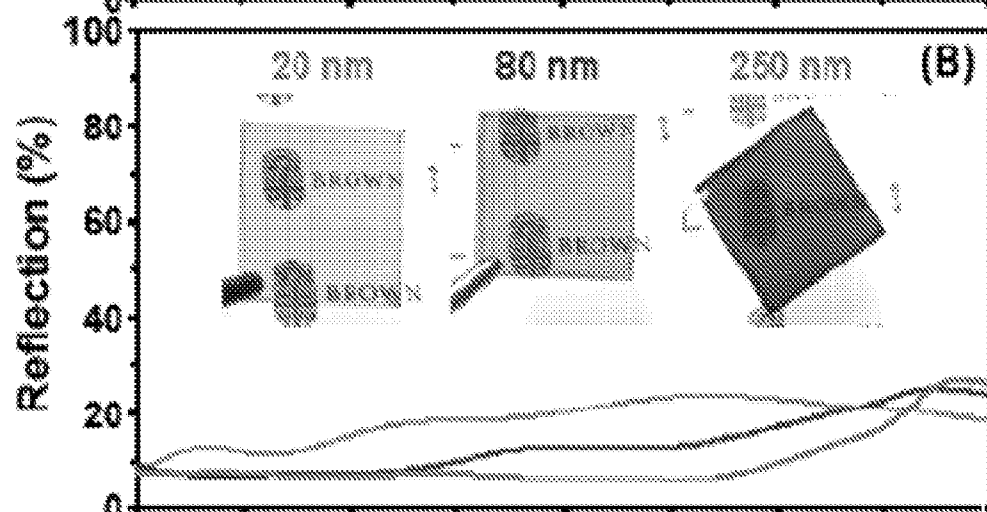


Figure 10B

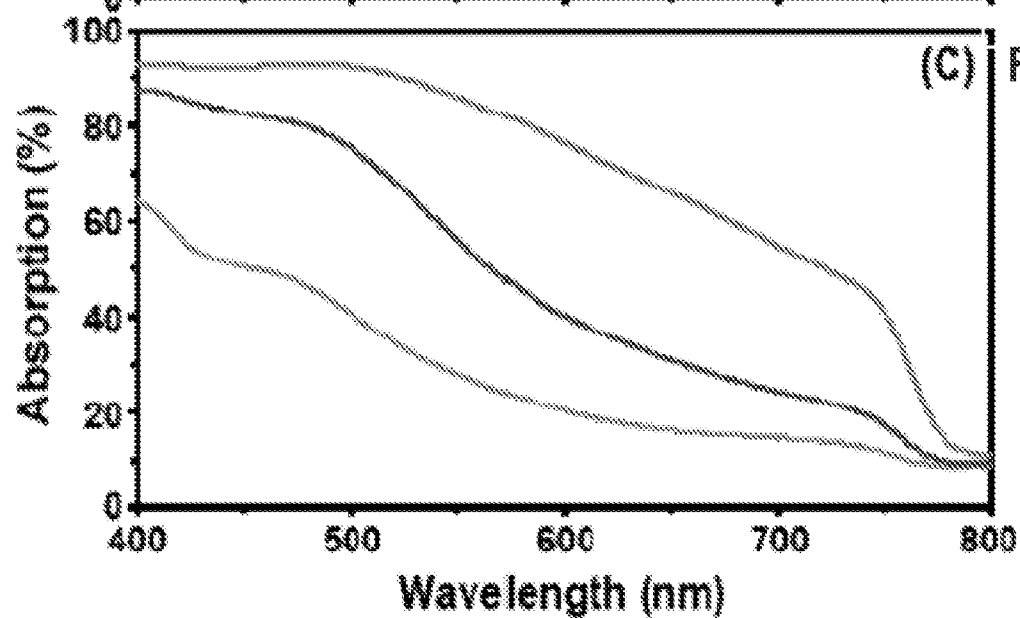


Figure 10C

Figure 11A

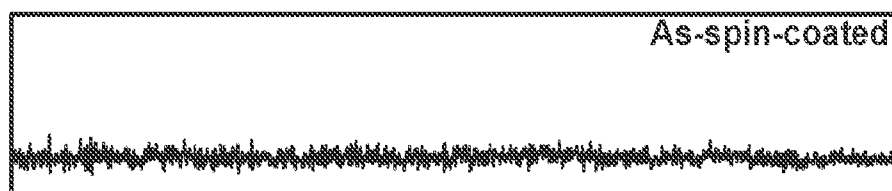


Figure 11B

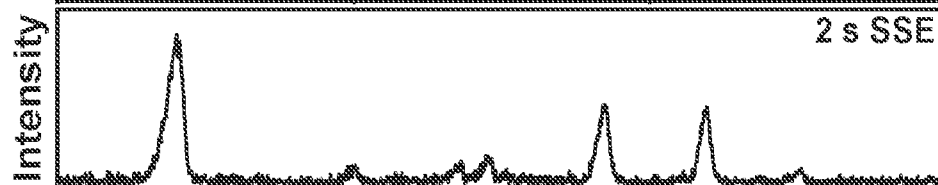


Figure 11C

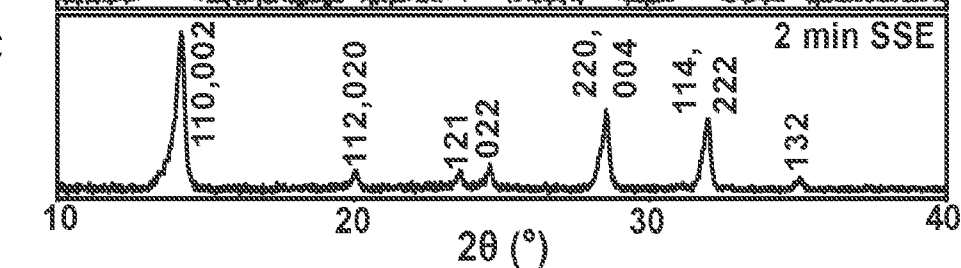


Figure 11D

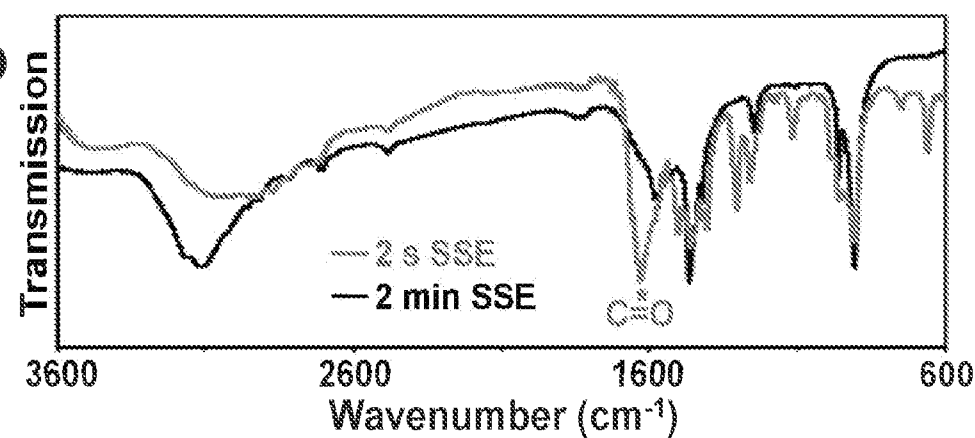


Figure 11E

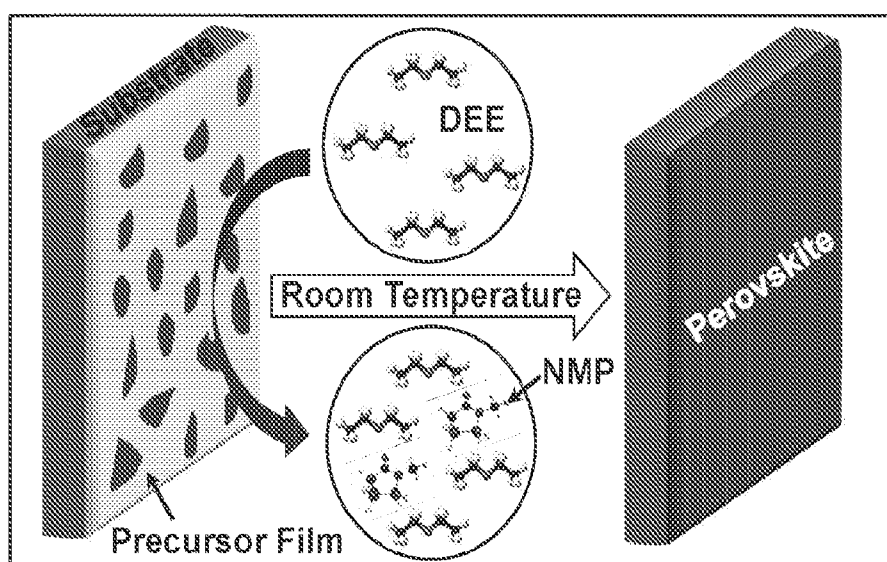


Figure 12A

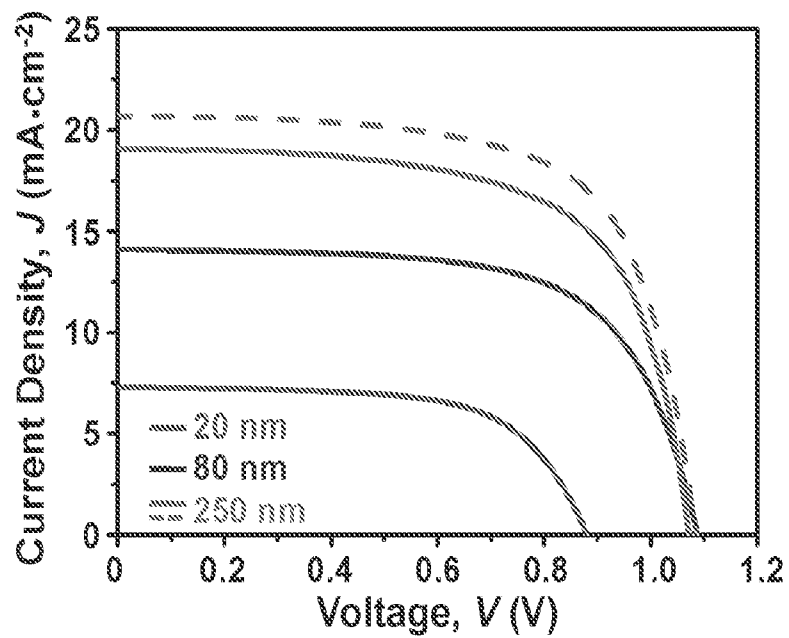


Figure 12B

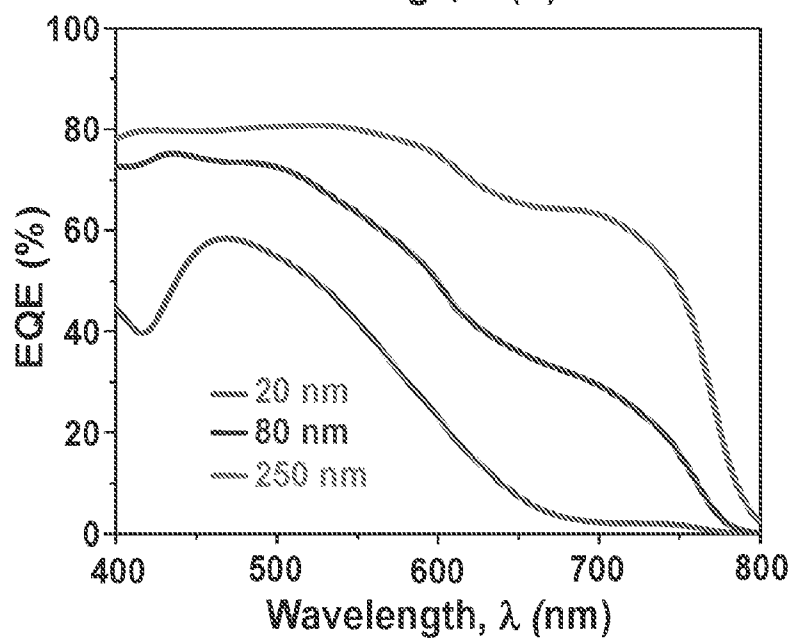


Figure 13

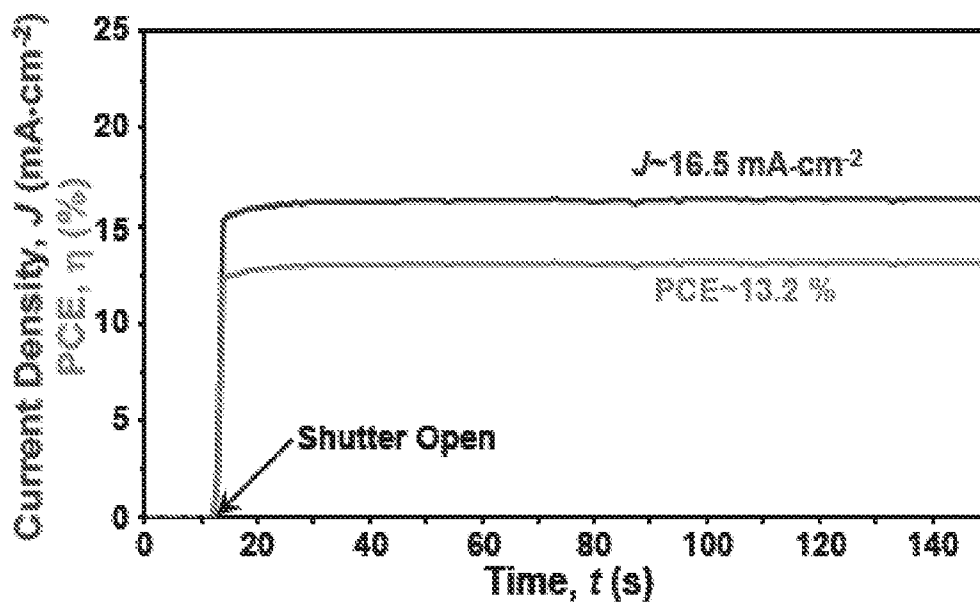


Figure 14

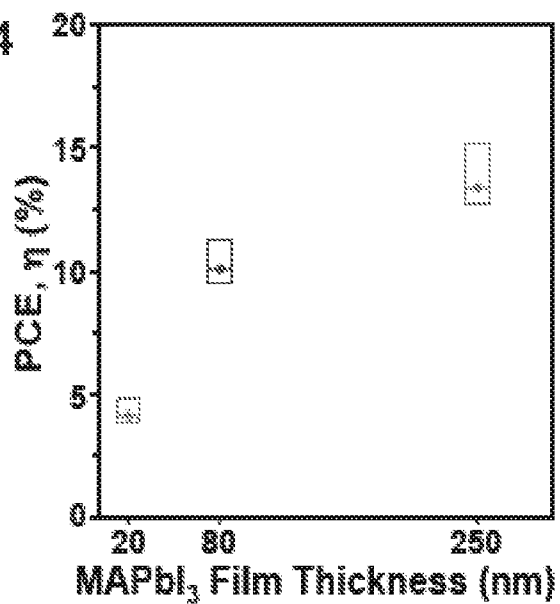


Figure 15A

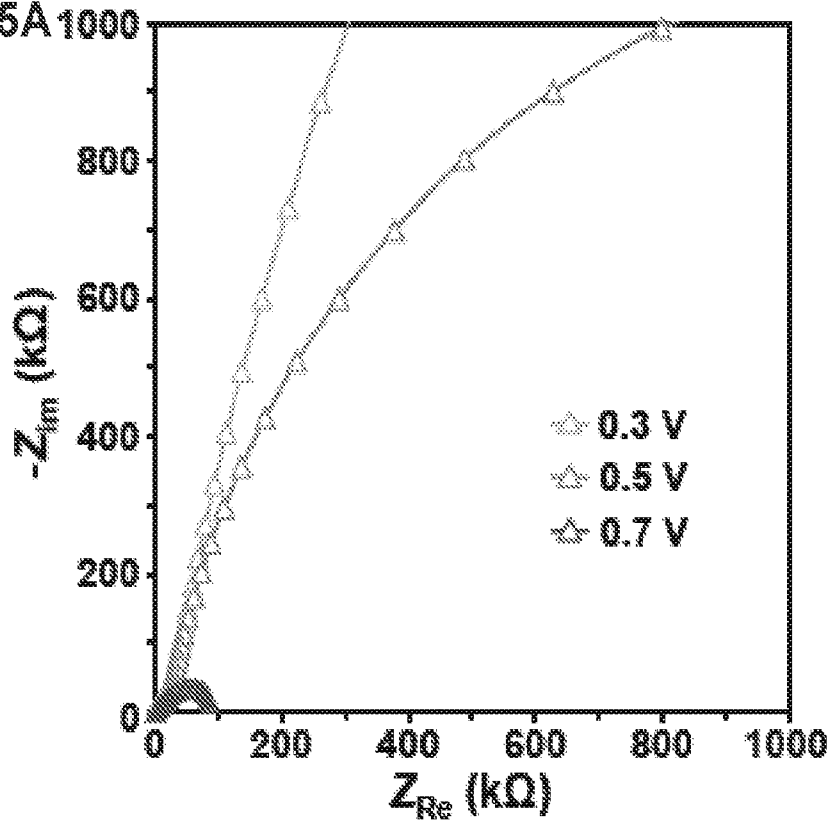


Figure 15B

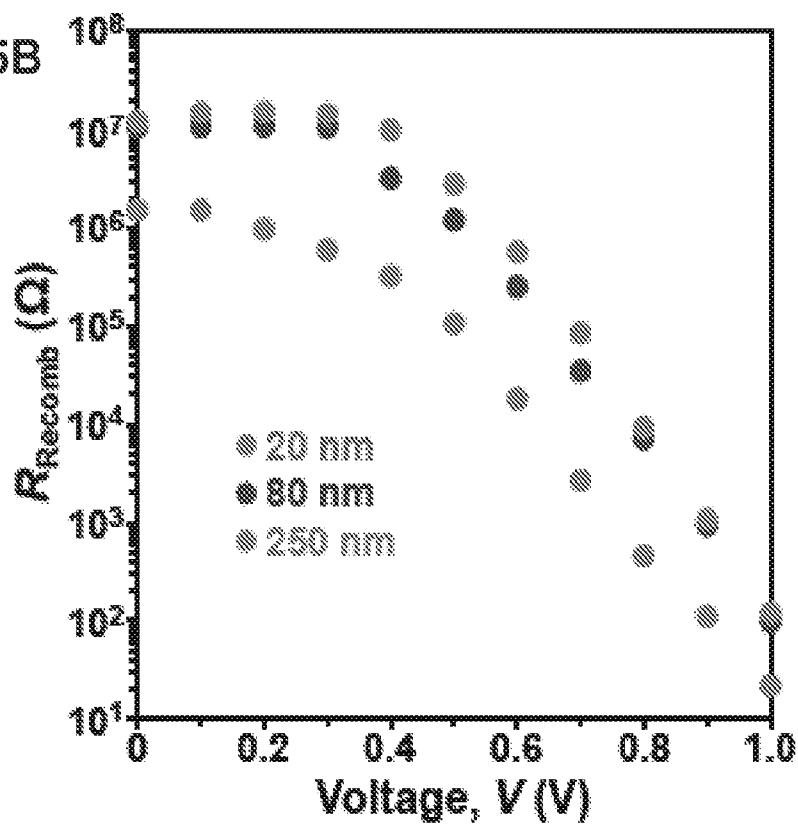


Figure 16A

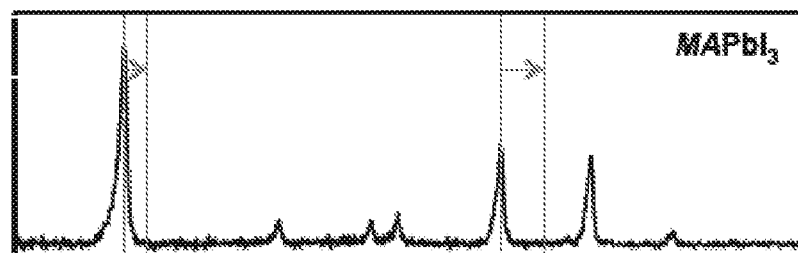


Figure 16B

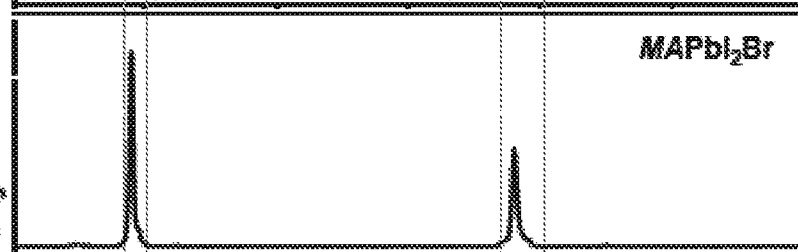


Figure 16C

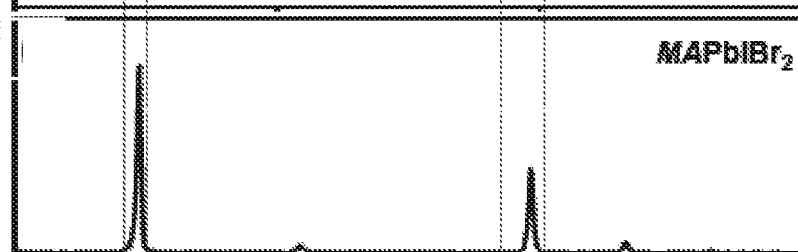
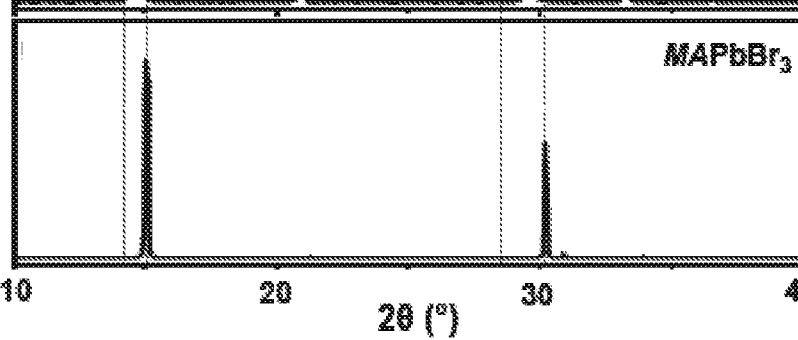


Figure 16D



INTERNATIONAL SEARCH REPORT

International application No.

PCT/US2015/061736

A. CLASSIFICATION OF SUBJECT MATTER

IPC(8) - B05D 5/12 (2016.01)

CPC - B05D 5/12 (2015.12)

According to International Patent Classification (IPC) or to both national classification and IPC

B. FIELDS SEARCHED

Minimum documentation searched (classification system followed by classification symbols)

IPC(8) - B05D 5/12; H01L 21/00, 31/18 (2016.01)

CPC - B05D 5/12; H01L 21/00, 31/18; Y02E 10/50, 10/54 (2015.12)

Documentation searched other than minimum documentation to the extent that such documents are included in the fields searched

USPC - 136/263; 427/74-76, 99.2; 438/57, 82; IPC(8) - B05D 5/12; H01L 21/00, 31/18; CPC - B05D 5/12; H01L 21/00, 31/18; Y02E 10/50, 10/54 (keyword delimited)

Electronic data base consulted during the international search (name of data base and, where practicable, search terms used)

Orbit, Google Scholar.

Search terms used: coated, coating, substrate, solvent, cosolvent, organometallic, pervoskites, extracted, extraction, precipitate, precipitated, precipitation, solar cell.

C. DOCUMENTS CONSIDERED TO BE RELEVANT

Category*	Citation of document, with indication, where appropriate, of the relevant passages	Relevant to claim No.
Y	US 2012/0111403 A1 (AHN et al) 10 May 2012 (10.05.2012) entire document	28
Y	US 5,866,471 A (BEPPU et al) 02 February 1999 (02.02.1999) entire document	28
A	US 2014/0256081 A1 (ALLIANCE FOR SUSTAINABLE ENERGY LLC) 11 September 2014 (11.09.2014) entire document	1-60
A	US 2013/0309613 A1 (CORNING INCORPORATED) 21 November 2013 (21.11.2013) entire document	1-60
A	US 8,617,642 B2 (JOO et al) 31 December 2013 (31.12.2013) entire document	1-60



Further documents are listed in the continuation of Box C.



See patent family annex.

* Special categories of cited documents:

"A" document defining the general state of the art which is not considered to be of particular relevance

"E" earlier application or patent but published on or after the international filing date

"L" document which may throw doubts on priority claim(s) or which is cited to establish the publication date of another citation or other special reason (as specified)

"O" document referring to an oral disclosure, use, exhibition or other means

"P" document published prior to the international filing date but later than the priority date claimed

"T" later document published after the international filing date or priority date and not in conflict with the application but cited to understand the principle or theory underlying the invention

"X" document of particular relevance; the claimed invention cannot be considered novel or cannot be considered to involve an inventive step when the document is taken alone

"Y" document of particular relevance; the claimed invention cannot be considered to involve an inventive step when the document is combined with one or more other such documents, such combination being obvious to a person skilled in the art

"&" document member of the same patent family

Date of the actual completion of the international search

12 January 2016

Date of mailing of the international search report

22 JAN 2016

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